

TPS2661x: 50 V, Universal 4 - 20 mA, ± 20 -mA Current Loop Protector with Input/Output Miswiring Protection

1 Features

- ± 50 -V operating voltage, ± 55 -V absolute maximum
- Integrated fixed bipolar 32-mA current limit
- Allows 2x current limit at startup
- 50% space savings compared to a typical discrete protection circuit
- Low R-on: 7.5- Ω typical
- Low I_q (< 100 nA) - current drawn from loop when powered from external supply
- Protection against miswiring conditions on IN and OUT
- Protection during signal line surge IEC61000-4-5 (with external TVS)
- Criteria-A EFT (IEC61000-4-4) immunity (with external TVS)
- Supports loop testing without supply (TPS26610 only)
- HART compliant
- Enable control
- S_{GOOD} for system health monitoring
- Thermal shutdown

2 Applications

- Factory automation and control – PLCs - analog input / output module
- Motor drives control
- HART inputs
- HVAC controllers
- UART IO protection
- Thermal controller

3 Description

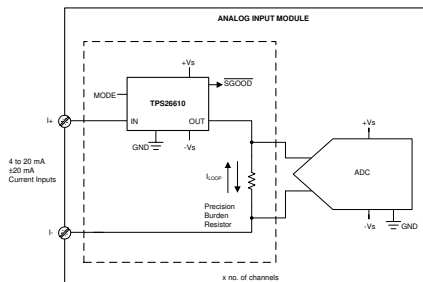
The TPS2661x is a compact, feature rich, fully integrated current loop protector suitable for analog inputs, analog outputs, sensor transmitters, HART Inputs and UART IO protection. It provides Universal Input protection for ± 20 mA, 0 to 20 mA, 4-20 mA. Low R_{ON} of 7.5 Ω minimizes drop in the current loop, thereby extending operating range and supporting operation even with lower voltage power supplies. The device can withstand and protect the loads from positive and negative supply voltages up to ± 50 V. The MODE pin allows flexibility to enable 2x current limit through the device to enable proper startup of two wire transmitters. Device is capable of operating from an external bipolar supply as low as ± 2.25 V to ± 20 V. It can also be powered from unipolar supplies as low as 3 V to 30 V. TPS26610 device features loop power mode to facilitate loop testing in un-powered state without $\pm V$ s supplies.

The device also protects the system from output side miswiring in Analog Outputs and sensor transmitters by turning off the current path. The internal robust protection control blocks along with the 50-V rating of the TPS2661x helps to protect against surge (IEC61000-4-5) and EFT (IEC61000-4-4) transients for signal lines. The device greatly reduces system footprint by its 2.9 mm \times 1.6 mm 8-pin SOT-23 package.

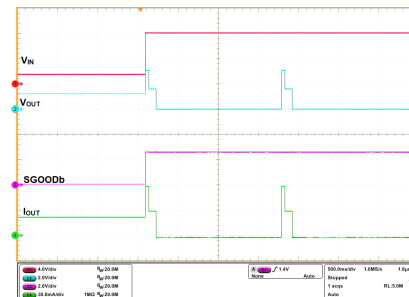
Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TPS26610	SOT-23 (8)	2.9 mm \times 1.6 mm
TPS26611		
TPS26612		

- (1) For all available packages, see the orderable addendum at the end of the data sheet.



Typical Circuit Schematic



Miswiring Protection on Input From Field Supply



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision A (March 2021) to Revision B (May 2021)	Page
• Removed preview note from TPS26611 and TPS26612 in the <i>Device Information</i> table	1
Changes from Revision * (November 2020) to Revision A (March 2021)	Page
• Changed status from "Advance Information" to "Production Data".....	1

5 Device Comparison Table

Part Number	EN Pin	Loop testing without $\pm V_s$ Supplies (Loop Power Mode)	Extended Overload Duration for First Overload Event	Application
TPS26610	No	Yes	No	Current Inputs. See Typical Application: Analog Input Protection for Current Inputs with TPS26610 .
TPS26611	Yes	No	No	Multiplexed voltage and current inputs. Analog outputs. See Typical Application: Analog Input Protection for Multiplexed Current and Voltage Inputs with TPS26611 .
TPS26612	Yes	No	Yes. Overload Expiry time is increased up to 5 sec (t_{AR_dis}).	Power supply protection for transmitters and Analog outputs. See Power Supply Protection of 2-Wire Transmitter with TPS26612 .

6 Pin Configuration and Functions

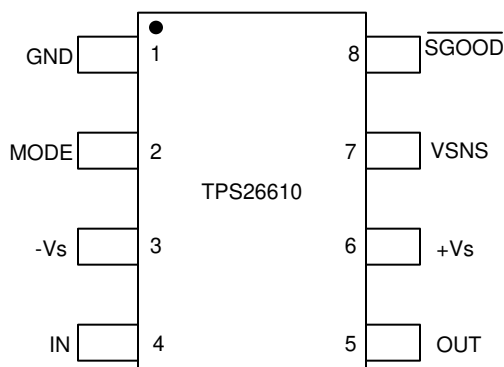


Figure 6-1. TPS26610 DDF Package 8-Pin SOT-23 Top View

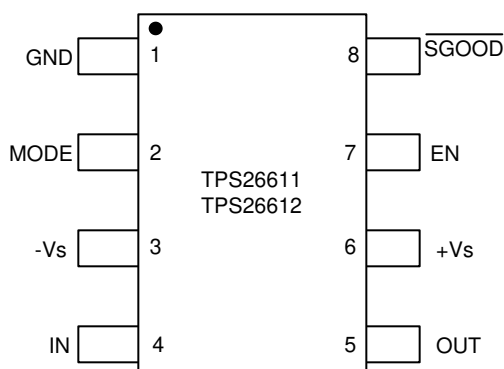


Figure 6-2. TPS26611 and TPS26612 DDF Package 8-Pin SOT-23 Top View

Table 6-1. Pin Functions

PIN		TYPE	DESCRIPTION
NO.	NAME		
1	GND	-	Reference ground for all internal voltages. Connect to GND of $\pm V_s$ Supply.
2	MODE	I	MODE selection pin for overload response. Sets current limit to I_{OL} , $2 \times I_{OL}$ or $2 \times I_{OL}$ with extended I_{OL} expiry time. See the Device Functional Modes for details.
3	-Vs	P	Negative supply for dual supply configurations. Connect to GND when using in single supply configuration.
4	IN	P	Signal / Power input.
5	OUT	P	Signal / Power output.
6	+Vs	P	Positive supply for powering device.
7	EN	I	For TPS26611 and TPS26612: Enable control. Pull EN low to turn off the device. EN has internal pull-up and it can be left floating to enable the device.
	VSNS	I	For TPS26610: Supply sensing input for transition to loop power mode. If not used, this can be left open or floating.
8	SGOOD	O	Signal good indicator pin. Whenever the device is within normal operating condition, SGOOD shows low indicating signal is good to read. This pin can also be used to drive an external LED to give a visual indication about the state of system.

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
IN, OUT, IN-OUT		-55	55	V
SGOOD, EN, MODE, VSNS		-0.3	5.5	V
+Vs		-0.3	32	V
-Vs		-22	0.3	V
I _{MODE} , I _{SGOOD} , I _{EN}	Source Current	Internally Limited		
I _{EN}	Sink Current	Internally Limited		
I _{SGOOD}			200	μA
T _J	Operating Junction temperature	-40	150	°C
	Transient Junction temperature	-65	T _(TSD)	
T _{stg}	Storage temperature	-65	150	

- (1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±750	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
IN, OUT	Voltage	-50		50	V
+Vs,	Supply Voltage	0		30	
-Vs		-20		0	V
EN, SGOOD, VSNS	Voltage	0		5	V
MODE		0		3	V
T _J	Operating Junction temperature	-40		125	°C

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TPS2661	UNIT
		DDF (SOT-23-THN)	
		8 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	117.8	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	57.6	°C/W
R _{θJB}	Junction-to-board thermal resistance	40.2	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	2.2	°C/W

7.4 Thermal Information (continued)

THERMAL METRIC ⁽¹⁾		TPS2661	UNIT
		DDF (SOT-23-THN)	
		8 PINS	
Ψ_{JB}	Junction-to-board characterization parameter	40	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

7.5 Electrical Characteristics

–40° C ≤ T_A = T_J ≤ +125° C, 2.25 V < +V_S < 30 V, –20 V < –V_S < 0 V, MODE = GND, $\overline{\text{SGOOD}}$ = Open, EN = 3.3 V (All voltages referenced to GND, (unless otherwise noted))

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SIGNAL INPUT (IN)						
V _(IN)	IN Signal Voltage		–50		50	V
I _Q	Sum of Leakage Curreent from IN and OUT pins to GND in normal operation	(–Vs) < V _{IN} , V _{OUT} < (+Vs - 0.35 V)	–0.1		0.1	μA
		(+Vs - 0.35 V) < V _{IN} , V _{OUT} < +Vs			1	uA
I _{QFLT}	Sum of leakage current from IN and OUT pins to –Vs pin during fault as percentage of loop current	V _{IN} > +Vs, Current Limit Operation			20	%
I _(OL)	Bipolar current limit	V _(IN) -V _(OUT) = ±1 V, –Vs connected to negative supply	±25	±32	±40	mA
	Unipolar Current limit	V _(IN) -V _(OUT) = +1 V, –Vs connected to GND	25	32	40	mA
I _(OL_Pulse)	Transient Pulse Over Current Limit	V _(IN) -V _(OUT) = +1.5 V, MODE = Floating	50	60	72	mA
I _(FASTRIP)	Fast-trip current limit	MODE = GND	±65		±165	mA
		MODE = Floating or 180 kΩ to GND	±140		±275	mA
I _{Off-Lkg-IN} + I _{Off-Lkg-OUT}	Sum of leakage current from IN and OUT pins in Off state (Source)	-12.5 V < V _{IN} <12.5 V; V _{OUT} = 0 V; EN = Low; +V _s = 15V; (–V _s) = -15 V (TPS26611 and TPS26612)	–9.75		–5.25	μA
		-12.5 V < V _{OUT} < 12.5 V; V _{IN} = 0 V; EN = Low; +V _s = 15V; (–V _s) = -15 V (TPS26611 and TPS26612)	–9.75		–5.25	μA
I _{Off-Lkg-IN}	Leakage current from IN pin in Off state (Source)	-12.5 V< V _{IN} <12.5 V; V _{OUT} = 0 V; EN = Low; +V _s = 15V; (–V _s) = -15 V (TPS26611 and TPS26612)	–6		–1	μA
I _{Off-Lkg-OUT}	Leakage current from OUT pin in Off state (Source)	-12.5 V < V _{OUT} < 12.5 V; V _{IN} = 0 V; EN = Low; +V _s = 15V; (–V _s) = -15 V (TPS26611 and TPS26612)	–6		–1	μA
Overvoltage and Undervoltage Cutoff for OUT and IN Pins						
V _{OUT_OVLO}	OUT Overvoltage Protection Threshold, Rising	For TPS26610 and TPS26611	(+Vs)+0.05		(+Vs)+0.30	V
		For TPS26612	(+Vs)+1		(+Vs)+1.50	V
V _{OUT_OVLO_hyst}	OUT Overvoltage Hysterises		30		75	mV
V _{O/I_UVLO}	OUT/IN Undervoltage Protection Threshold, Falling		(–Vs)-0.40		(–Vs)-0.20	V
V _{O/I_UVLO_hyst}	OUT/IN undervoltage Hysterises		30		75	mV

7.5 Electrical Characteristics (continued)

–40° C ≤ T_A = T_J ≤ +125° C, 2.25 V < +V_S < 30 V, –20 V < –V_S < 0 V, MODE = GND, $\overline{\text{SGOOD}}$ = Open, EN = 3.3 V (All voltages referenced to GND, (unless otherwise noted))

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
POWER SUPPLY PINS (+V_S/–V_S)					
V _(+V_S)	+V _S Supply Operating Voltage	For TPS26610 and TPS26611 only	2.25	30	V
V _(+V_S)	+V _S Supply Operating Voltage	TPS26612 only	4	30	V
V _(–V_S)	–V _S Supply Operating Voltage		–20	0	V
V _{S_DIFF}	Difference between +V _S and –V _S		3	50	V
I _(+V_S)	Current sourced from +V _S supply to GND in normal operation	$\overline{\text{SGOOD}}$ = Floating	1.07	1.65	mA
I _(+V_S)	Current sourced from +V _S supply to GND in fault operation	$\overline{\text{SGOOD}}$ = Floating	1.2	1.75	mA
I _(–V_S)	Current sunk by –V _S supply from GND			0.2	mA
I _{VS_OFF}	OFF State Supply Current	EN = Low (TPS26611/12 only)		0.27	mA
Loop Testing V_S/–V_S UNPOWERED (TPS26610 only)					
V _{(IN-OUT)no_Vs}	Current Loop Testing : IN to OUT Voltage drop	+/-20mA current through IN pin	±5	±8.5	V
I _{Qno_Vs}	Percentage of forced IN current going to –V _S pin			20	%
I _{OL_noVs}	No supply current limit		±22	±45.5	mA
PASS FET					
R _{ON}	IN to OUT total ON resistance	–40 °C < T < 125 °C, I _(IN) < Overload Current	4.8	7.5	12.5 Ω
ENABLE (EN) TPS26611 and TPS26612 only					
V _(ENR)	EN Rising Threshold			1.72	V
V _(ENF)	EN Falling Threshold		1		V
I _(EN_LKG)	EN Leakage Current (Sink)	V _(EN) = 5.5 V		10	μA
I _(EN_LKG)	EN Leakage Current (Source)	V _(EN) = 0 V	–10		μA
V _(EN)	EN Open Circuit Voltage	I _(EN) = –0.1 μA	2.1	2.5	V
VSNS (Supply Sensing) TPS26610 only					
V _(SNSR)	VSNS Rising threshold			1.72	V
V _(SNSF)	VSNS Falling threshold		1		V
SIGNAL GOOD ($\overline{\text{SGOOD}}$)					
V _{OH_SGOOD}	$\overline{\text{SGOOD}}$ Output Level, HIGH	(+V _S) ≤ 2.5 V, 0 mA < I _{SGOOD} < 1 mA	0.8 x (+V _S)	(+V _S)	V
V _{OH_SGOOD}	$\overline{\text{SGOOD}}$ Output Level, HIGH	(+V _S) > 2.5V, 0 mA < I _{SGOOD} < 1 mA	2	3	V
R _{SGOOD}	$\overline{\text{SGOOD}}$ pull down impedance	0 μA < I _{SGOOD} < 200 μA		6.3	kΩ
MODE					
I _(MODE)	MODE Source Current		1.55	2	2.4 μA
R _{MODE}	Mode Selection Resistor			180	kΩ

7.5 Electrical Characteristics (continued)

–40° C ≤ T_A = T_J ≤ +125° C, 2.25 V < +V_S < 30 V, –20 V < –V_S < 0 V, MODE = GND, $\overline{\text{SGOOD}}$ = Open, EN = 3.3 V (All voltages referenced to GND, (unless otherwise noted))

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
THERMAL SHUTDOWN					
T _(TSD)	Thermal Shutdown (TSD) threshold, Rising		160		°C
T _(TSDHyst)	Thermal Shutdown (TSD) Hysterises		11		°C
HART					
BW	Input small signal bandwidth	–25 mA < I _{IN} < 25 mA, ΔI _{IN} = 1 mA _{pp} at 1-kΩ	10		kHz

7.6 Timing Requirements

–40° C ≤ T_A = T_J ≤ +125° C, 2.25 V < +V_S < 30 V, –20 V < –V_S < 0 V, MODE = GND, $\overline{\text{SGOOD}}$ = Open, EN = 3.3V (All voltages referenced to GND, (unless otherwise noted))

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{ON_dly}	Turn ON delay with V _S /–V _S supply	Delay from +V _S /–V _S supply applied to FET on, EN = Floating	120		μs
t _{OFF_dly}	Turn OFF delay with +V _S /–V _S supply	Delay from +V _S /–V _S supply removed to FET off, EN = Floating		10	μs
t _{ON_EN_dly}	Turn ON delay with EN pin	+V _S /–V _S supply present, Delay from EN HIGH to FET on,	120		μs
t _{OFF_EN_dly}	Turn OFF delay with EN pin	+V _S /–V _S supply present, Delay from EN LOW to FET off		10	μs
t _{OL}	Overload Current Limit response time	Load transient from 20 mA to 50 mA. Time from Load Transient to Current coming within 20% of I _{OL} .	30	55	μs
t _{OL_PULSE}	Pulse Overload Current Limit response time	Load transient from 20 mA to 80 mA. Time from Load Transient to Current coming within 20% of I _{OL_Pulse}	20	50	μs
t _{FASTrip}	Fast-Trip Response Time	MODE = GND, Current exceeding 120mA to FET off		5	μs
		MODE = 180-kΩ to GND or Open, Current exceeding 240 mA to FET off		5	μs
T _{SG_Deg glitch}	$\overline{\text{SGOOD}}$ Deglitch Delay	Deglitch delay during $\overline{\text{SGOOD}}$ assertion	685		μs
		Deglitch delay during $\overline{\text{SGOOD}}$ de-assertion		1.3	ms
t _{OUT_OV_CUT}	OUT OVLO Cutoff detection-time	V _(OUT) ↑ 100 mV above V _{OUT_OVLO} to FET OFF	1	5	μs
t _{O/I_UV_CUT}	OUT OR IN UVLO Cutoff detection-time	OUT/IN ↓ 100 mV below V _{O/I_UVLO} to FET OFF	1	5	μs
t _{OUT_CUT_Rec}	OUT Cutoff recovery time	V _(OUT) ↓ 100 mV below V _{OUT_OVLO_hyst} to FET ON	21		μs
t _{O/I_CUT_Rec}	IN OR OUT Cutoff recovery time	OUT/IN ↑ 100 mV above V _{O/I_UVLO_hyst} to FET ON	23.5		μs
t _{OL_Expiry}	Overload Current Limit expiry time	Load transient from 20 mA to 50 mA	100		ms
t _{OL_Pulse_Expiry}	Pulse Overload Current expiry	Load transient from 20 mA to 100 mA	50		ms
t _{OL_Extend}	I _{OL} < I < I _{OL_PULSE} expiry timer		5.00		s
t _{RETRY1}	Auto Retry Timer 1		0.80		s
t _{RETRY2}	Auto Retry Timer 2		1.60		s

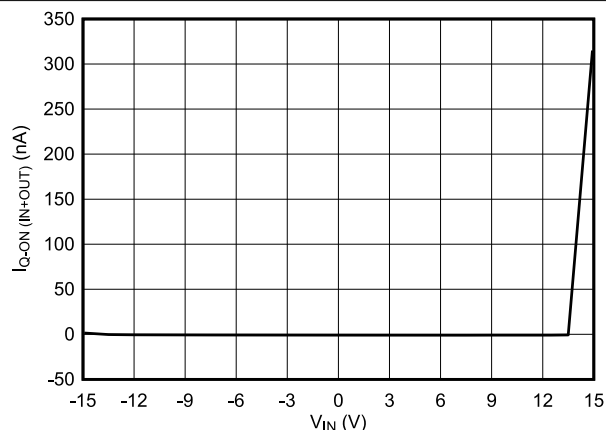
7.6 Timing Requirements (continued)

$-40^{\circ}\text{C} \leq T_A = T_J \leq +125^{\circ}\text{C}$, $2.25\text{ V} < +V_S < 30\text{ V}$, $-20\text{ V} < -V_S < 0\text{ V}$, $\text{MODE} = \text{GND}$, $\overline{\text{SGOOD}} = \text{Open}$, $\text{EN} = 3.3\text{V}$ (All voltages referenced to GND, (unless otherwise noted))

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{\text{AR_dis}}$	Auto Retry disabled time (TPS26612 only)			5		s

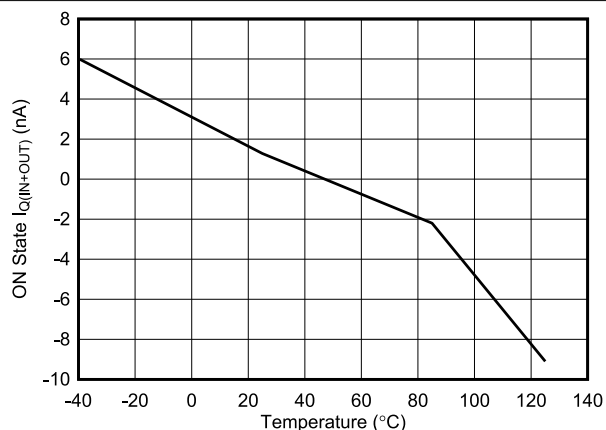
7.7 Typical Characteristics

+Vs = 15 V; -Vs = -15 V, MODE = OPEN, $\overline{\text{SGOOD}}$ = OPEN; EN/VSNS = OPEN; T_A = 25° C (unless otherwise noted)



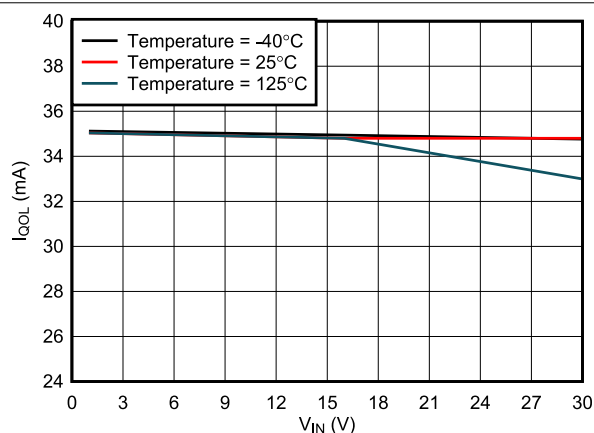
+Vs = 15 V; -Vs = GND; $V_{IN} = V_{OUT}$

Figure 7-1. $I_{Q-ON} (IN+OUT)$ vs V_{IN} in Normal Operation



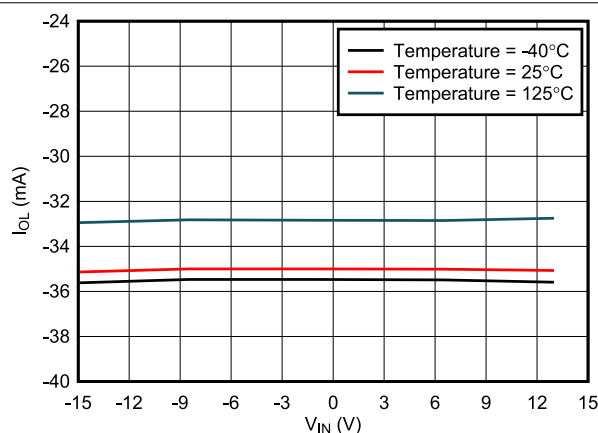
$V_{IN} = V_{OUT} = 0 \text{ V}$

Figure 7-2. $I_Q (IN+OUT)$ vs Temperature in Normal Operation



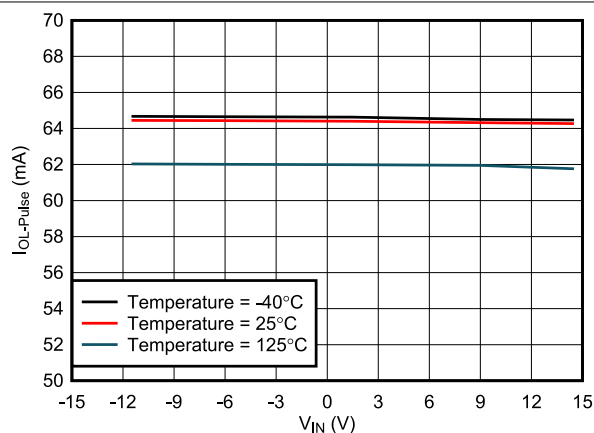
+Vs = 30 V; -Vs = GND; $V_{IN} = V_{OUT} + 1 \text{ V}$

Figure 7-3. I_{OL} vs V_{IN} for $I_{OUT} > 0$



$V_{IN} = V_{OUT} - 1 \text{ V}$

Figure 7-4. I_{OL} vs V_{IN} for $I_{OUT} < 0$



$V_{IN} = V_{OUT} + 1.5 \text{ V}$; MODE = Open or 180 k Ω

Figure 7-5. $I_{OL-Pulse}$ vs V_{IN}

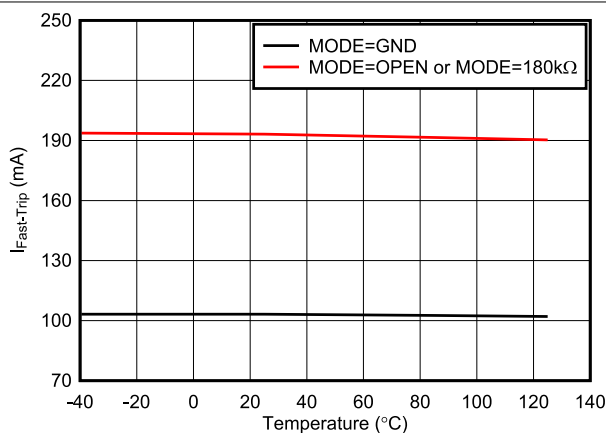


Figure 7-6. $I_{Fast-Trip}$ vs Temperature for $I_{OUT} > 0$

7.7 Typical Characteristics (continued)

+Vs = 15 V; -Vs = -15 V, MODE = OPEN, SGOOD = OPEN; EN/VSNS = OPEN; T_A = 25° C (unless otherwise noted)

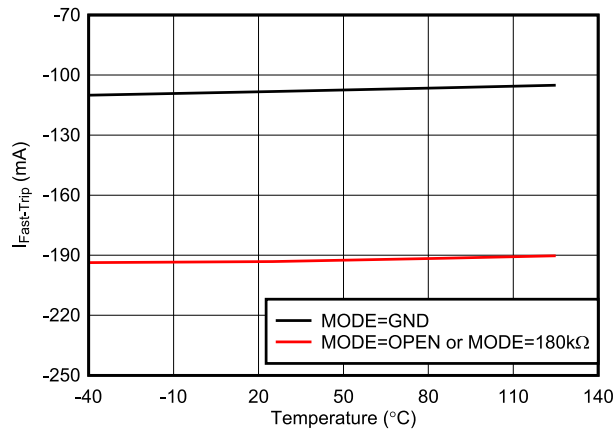


Figure 7-7. I_{Fast-Trip} vs Temperature for I_{OUT} < 0

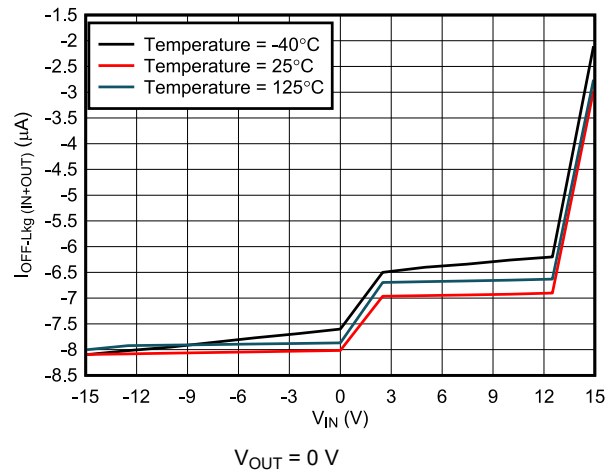


Figure 7-8. (I_{OFF-Leakage-IN} + I_{OFF-Leakage-OUT}) vs V_{IN}

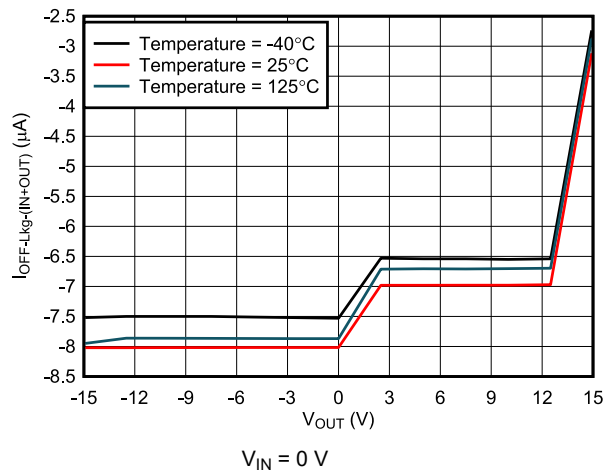


Figure 7-9. (I_{OFF-Leakage-IN} + I_{OFF-Leakage-OUT}) vs V_{OUT}

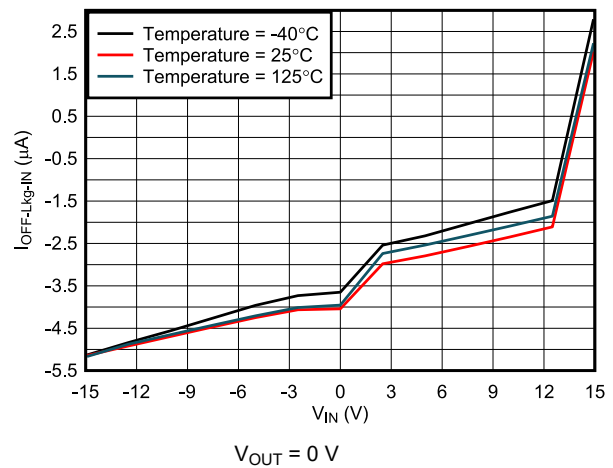


Figure 7-10. I_{OFF-Leakage-IN} vs V_{IN}

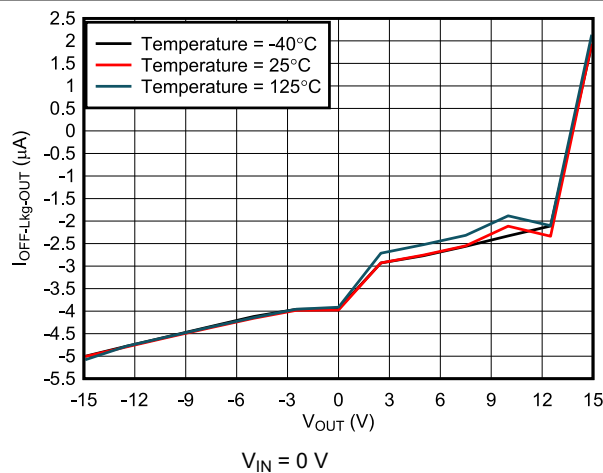


Figure 7-11. I_{OFF-Leakage-OUT} vs V_{OUT}

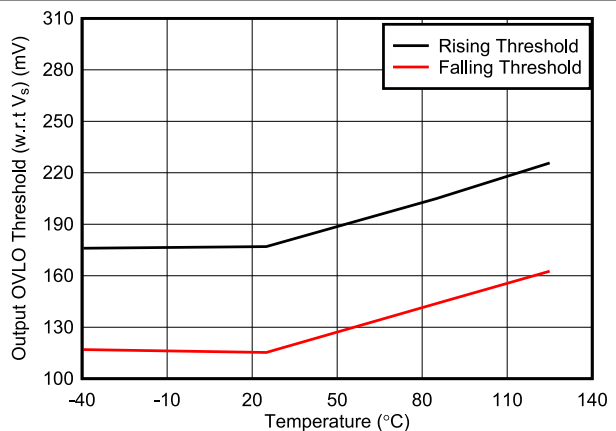


Figure 7-12. OUT OVLO Thresholds (w.r.t V_S) vs Temperature for TPS26611 and TPS26610

7.7 Typical Characteristics (continued)

+Vs = 15 V; -Vs = -15 V, MODE = OPEN, SGOOD = OPEN; EN/VSNS = OPEN; T_A = 25° C (unless otherwise noted)

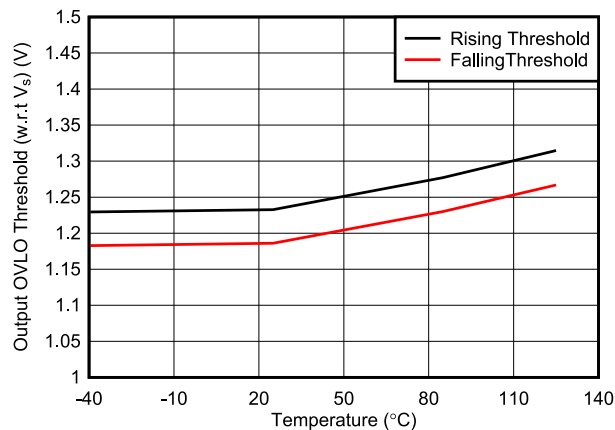


Figure 7-13. OUT OVLO Thresholds (w.r.t Vs) vs Temperature for TPS26612

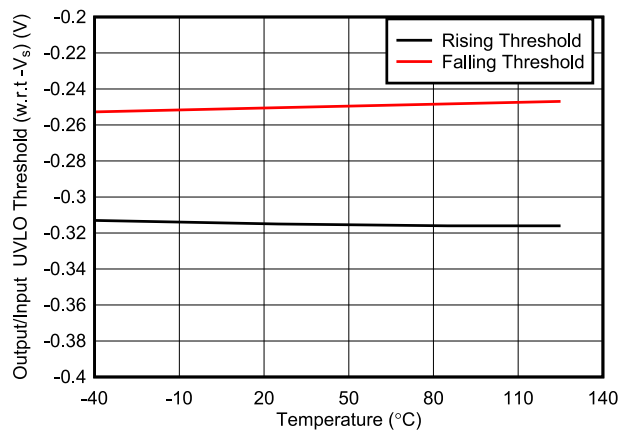


Figure 7-14. OUT and IN UVLO Thresholds (w.r.t -Vs) vs Temperature

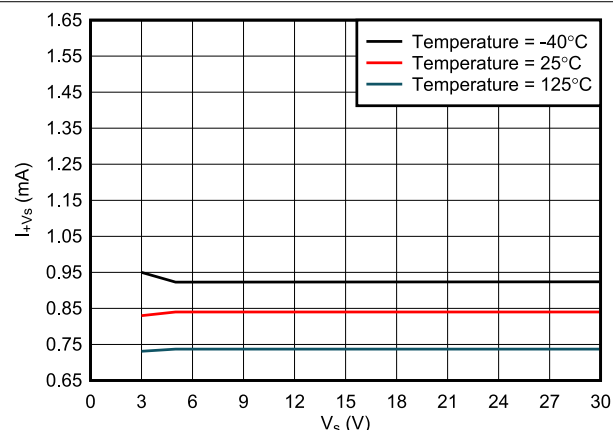


Figure 7-15. I_{Vs} vs Vs in ON State

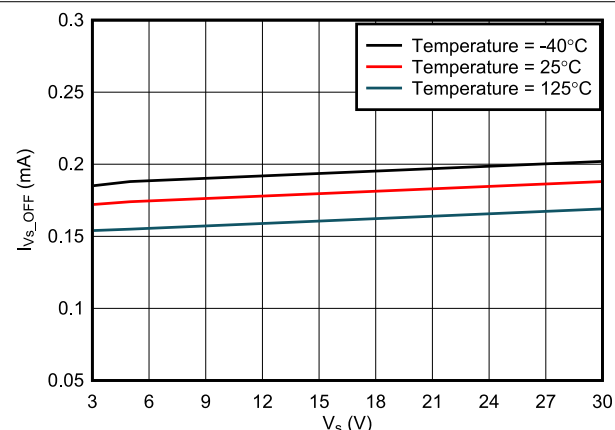


Figure 7-16. I_{Vs} vs Vs in OFF State (EN = 0) for TPS26611 and TPS26612

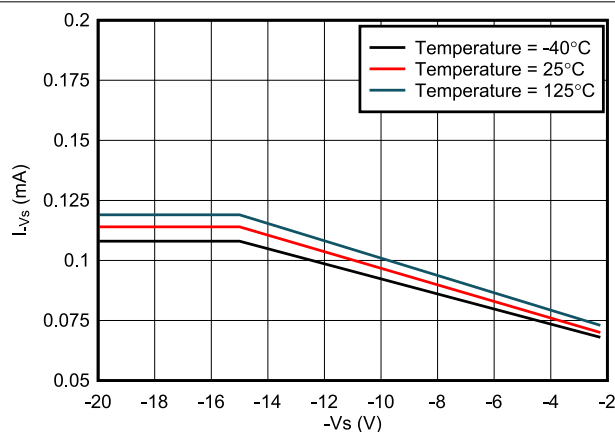


Figure 7-17. I_{Vs} vs -Vs in ON State

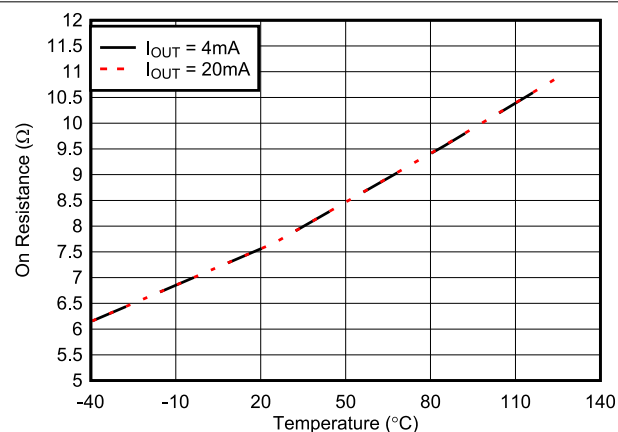


Figure 7-18. R_{ON} vs Temperature

7.7 Typical Characteristics (continued)

+Vs = 15 V; -Vs = -15 V, MODE = OPEN, SGOOD = OPEN; EN/VSNS = OPEN; T_A = 25° C (unless otherwise noted)

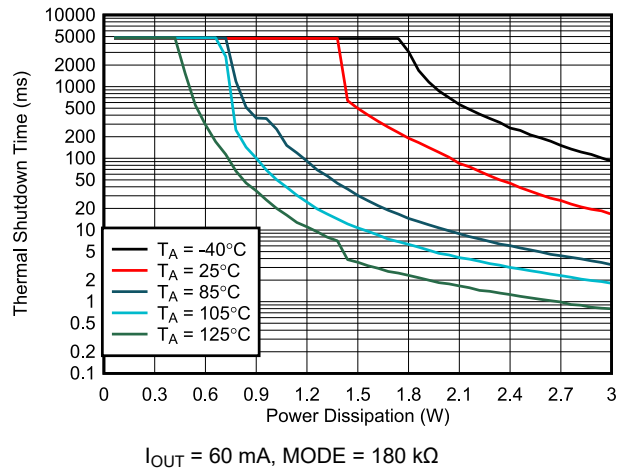


Figure 7-19. Thermal shutdown time vs Power Dissipation

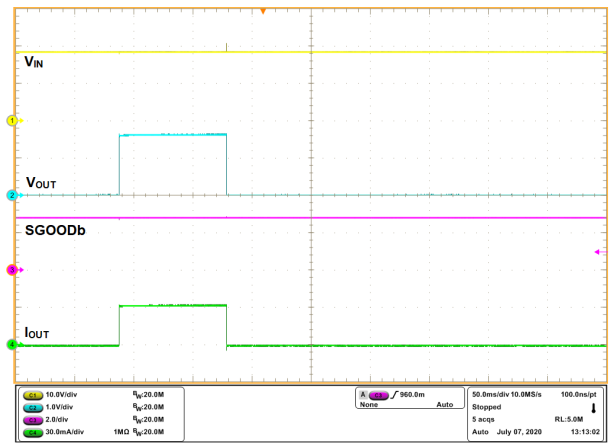


Figure 7-20. Current Limit with MODE = GND

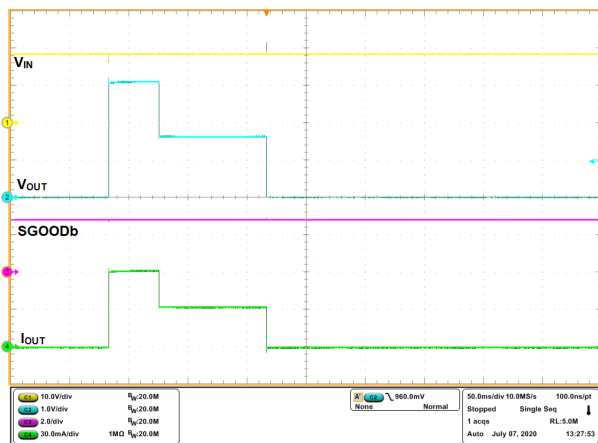


Figure 7-21. Current Limit with MODE = OPEN

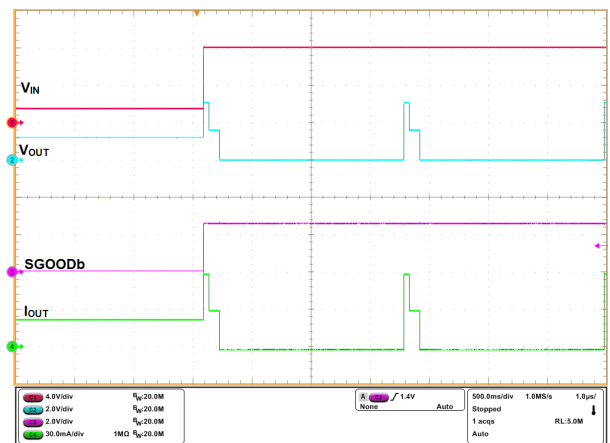


Figure 7-22. Auto Retry with MODE = 180 k Ω

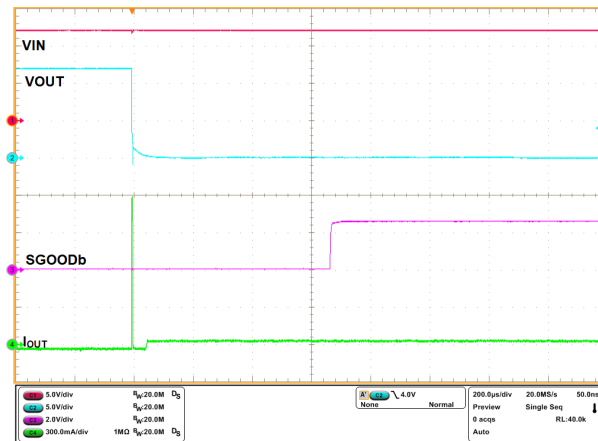


Figure 7-23. Fast-Trip Protection

8 Detailed Description

8.1 Overview

The TPS2661x is a family of devices providing complete protection for current inputs, voltage inputs/outputs and sensor supply in industrial and process automation systems. The device supports both unipolar 4 - 20-mA current loops and bipolar ± 20 -mA current loops. TPS26610 is tailored for current inputs. The device can be powered from an external supply and draws < 100-nA maximum current from the current loop enabling design of high accuracy analog input systems. The devices feature an accurate 32 mA current limit which enables using low power components in the loop like the sense resistors which reduces the overall system size and cost. TPS26611 is specifically tailored for universal current inputs, voltage/current multiplexed inputs while TPS26612 is tailored for protection of two wire sensor transmitters. TPS2661x devices feature a configurable MODE pin to allow higher current for powering up of a variety of two wire transmitters. TPS26611 also has enable control for designing V/I multiplexed analog inputs or universal Analog Input-Output modules. The device also features a Signal Good output to indicate if there is a valid current input. The signal good pin goes high in the event of any fault or during startup of the system if there is an inrush current. The device also protects the system from Output miswiring in Analog Output modules or sensor transmitters by cutting off the current path if the OUT pin goes outside the $\pm V_S$ supply rails.

The robust protection of the TPS2661x along with its ± 50 -V rating helps to simplify the system designs for the surge compliance. TPS2661x devices are immune to noise tests like Electrical Fast Transients that are common in industrial applications and these devices also simplify the system design for protection from surge transients (IEC61000-4-5).

8.2 Functional Block Diagram

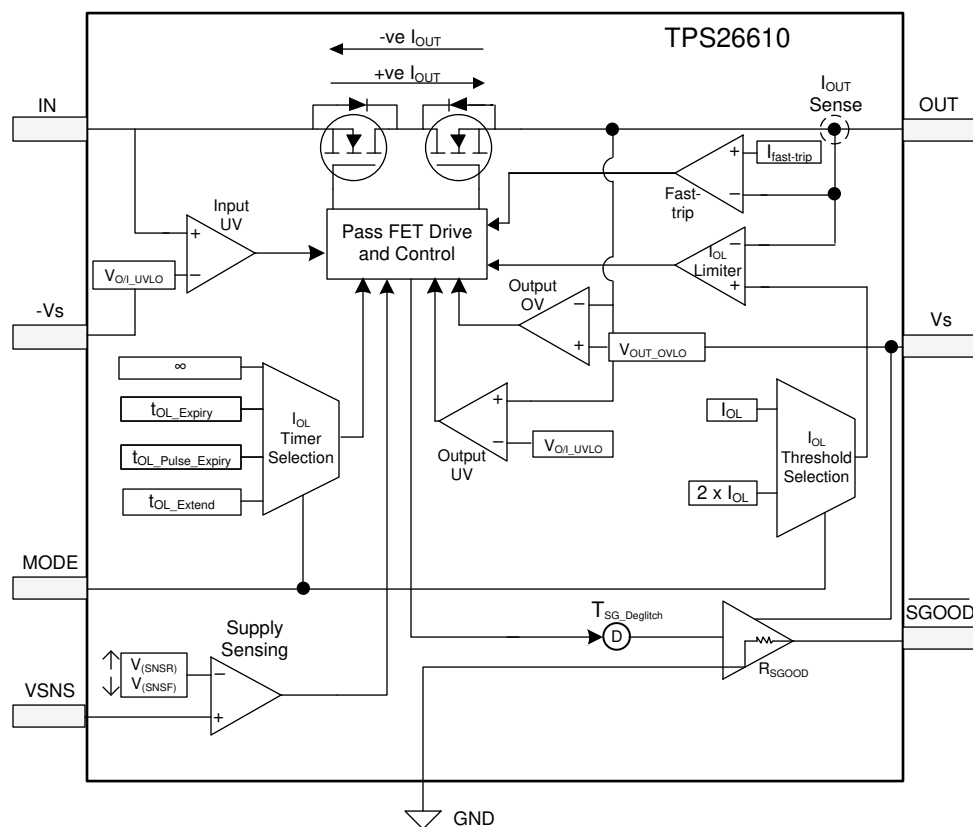


Figure 8-1. Functional Block Diagram for TPS26610

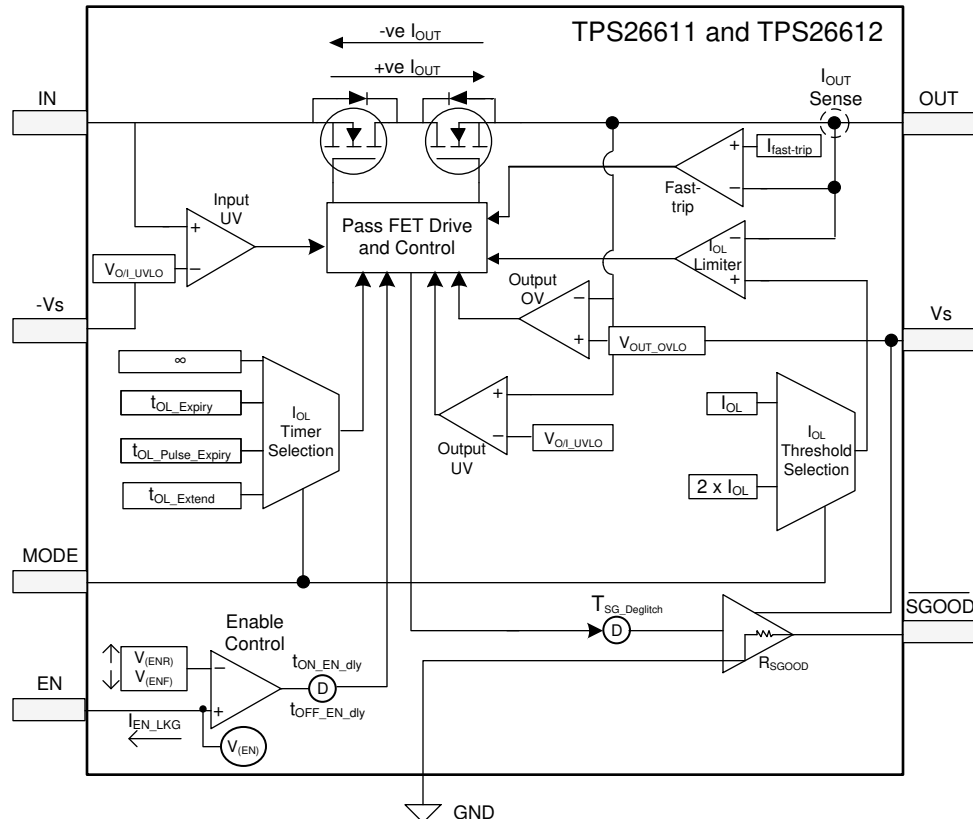


Figure 8-2. Functional Block Diagram for TPS26611 and TPS26612

8.3 Feature Description

8.3.1 Overload Protection and Fast-Trip

The TPS2661x devices feature a fixed I_{OL} : 32-mA typical, bidirectional current limit. For use in unipolar systems like 4-20-mA current loops where negative current is not desired, connect $-V_S$ to GND pin to cutoff when there is a flow of reverse current (OUT to IN). If the current tries to exceed the I_{OL} limit, the device regulates the current and eventually reducing the output voltage. Overload current threshold and time for overload protection can be selected by MODE pin. See [Device Functional Modes](#) for details. The power dissipation across the device during current regulation will be $(V_{IN} - V_{OUT}) \times I_{OUT}$ and this could heat up the device and lead to thermal shutdown. After thermal shutdown device goes into auto retry. The mode pin selects the auto retry period. See [Table 8-2](#) and [Figure 8-21](#) for selection of auto retry period.

The TPS2661x devices also feature a fast trip comparator. During fast transient events like output short circuit, miswiring, hotplug, etc the current through the device increases rapidly. Due to limited bandwidth, the current limit amplifier cannot respond quickly to these events. Hence the fast-trip comparator architecture is included for fast turn OFF of the internal FET during these events. The device turns off the internal FETs within a time of $t_{(FASTTRIP)}$. See [Timing Requirements](#) in Specifications for $t_{(FASTTRIP)}$. The fast-trip circuit holds the internal FET off for a short duration (50 μ s), after which the device turns back on slowly, allowing the current-limit loop to regulate the output current to current limit as per MODE pin configuration. [Figure 8-3](#) and [Figure 8-5](#) illustrate the current limit behavior of TPS2661x devices. [Figure 8-6](#) illustrates the fast-trip protection of TPS2661x devices and [Figure 8-7](#) illustrates the auto-retry behavior in overload fault.

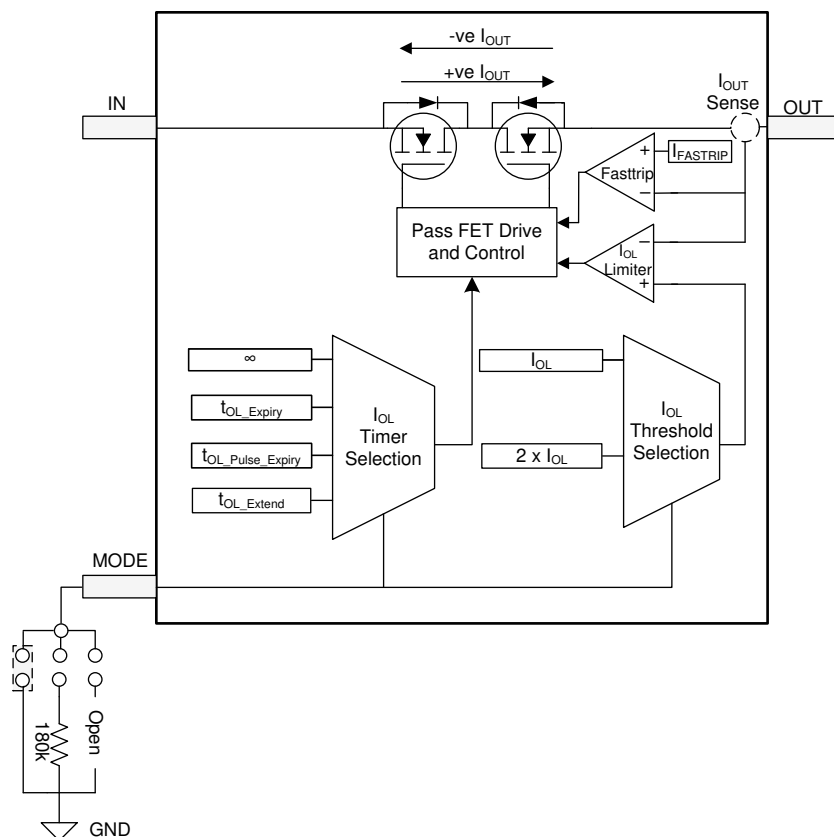
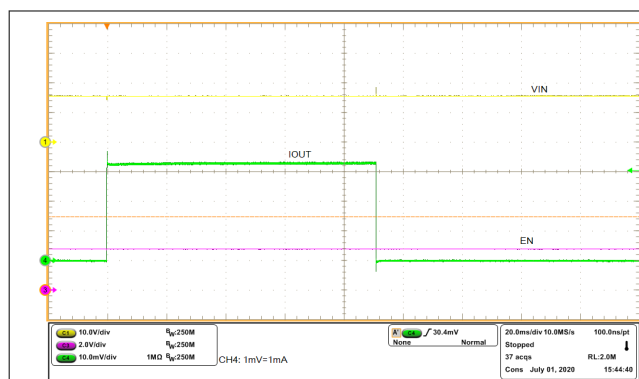
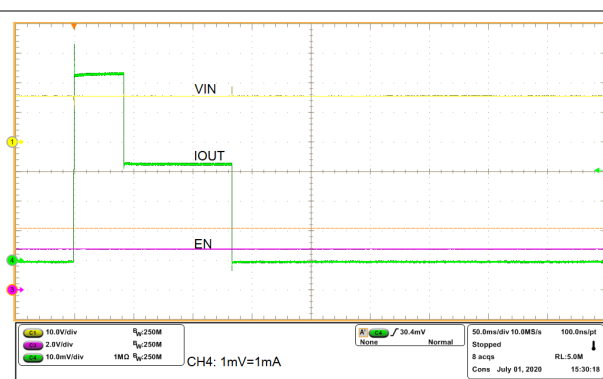
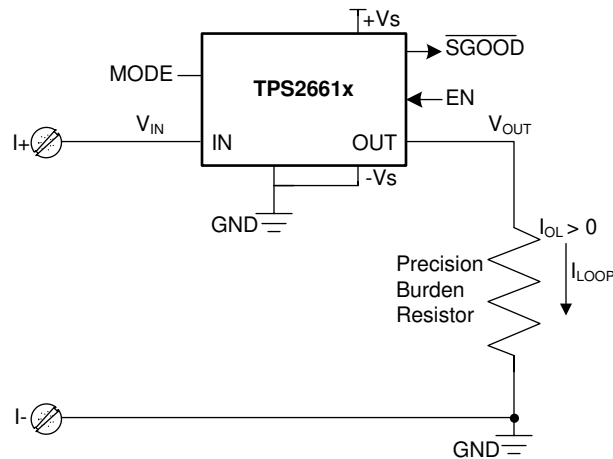


Figure 8-3. Overload Protection and Fast-Trip

Figure 8-4. Current Limit Behavior for $I_{OUT} < 2 \times I_{OL}$ with $MODE = GND$ Figure 8-5. Current Limit Behavior for $I_{OUT} > 2 \times I_{OL}$ with $MODE = 180 \text{ k}\Omega$



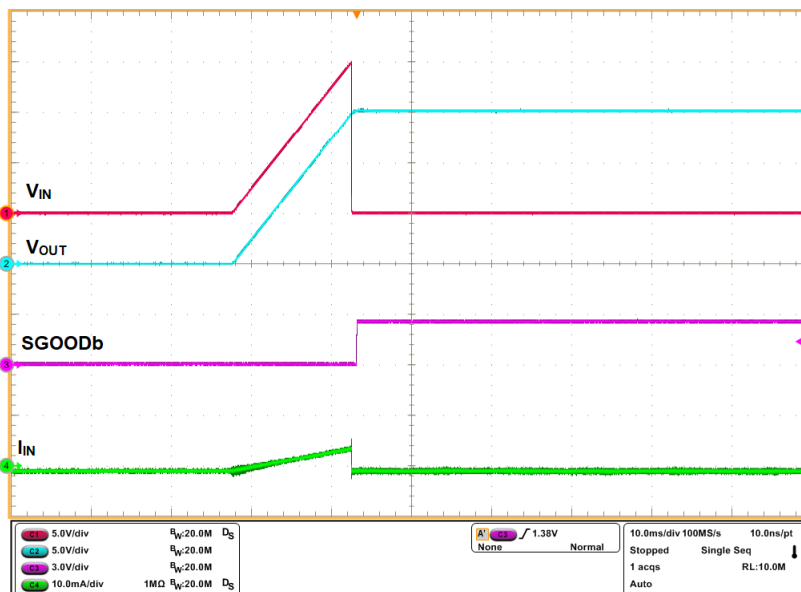


Figure 8-9. Output Over-Voltage Protection

8.3.3.2 Output or Input Under-Voltage

The TPS2661x devices provide protection from under-voltage events on IN and OUT pins by turning off the internal Pass FETs and cutting off the signal path whenever V_{OUT} or V_{IN} goes below V_{O/I_UVLO} threshold. The signal path through TPS2661x is restored again when V_{OUT} or V_{IN} goes above $[V_{O/I_UVLO} - V_{O/I_UVLO_Hyst}]$ value. The device turns off the internal FETs within a time of t_{O/I_UV_CUT} after output or input voltage has gone below V_{O/I_UVLO} threshold. The device recovers from output or input under-voltage within a time of $t_{OUT_CUT_Rec}$ after output or input voltage has gone above $[V_{O/I_UVLO} - V_{O/I_UVLO_Hyst}]$ voltage. See [Timing Requirements](#) in Specifications for t_{O/I_UV_CUT} and $t_{OUT_CUT_Rec}$.

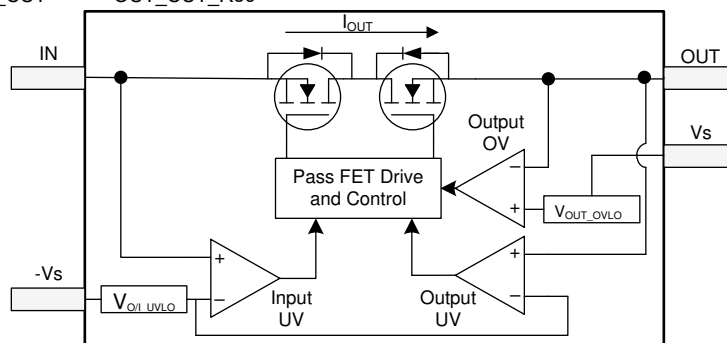
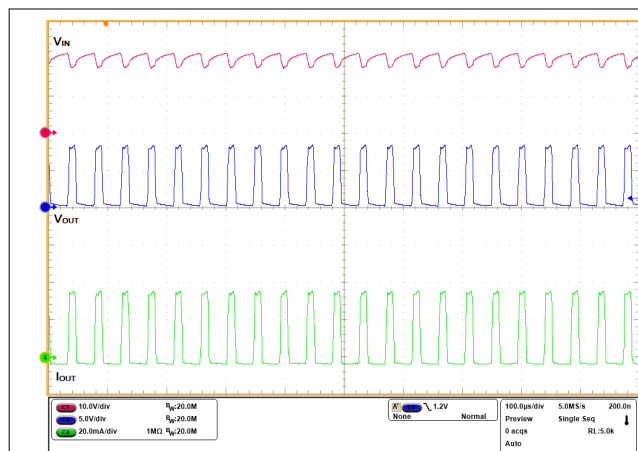


Figure 8-10. Output/Input Cutoff

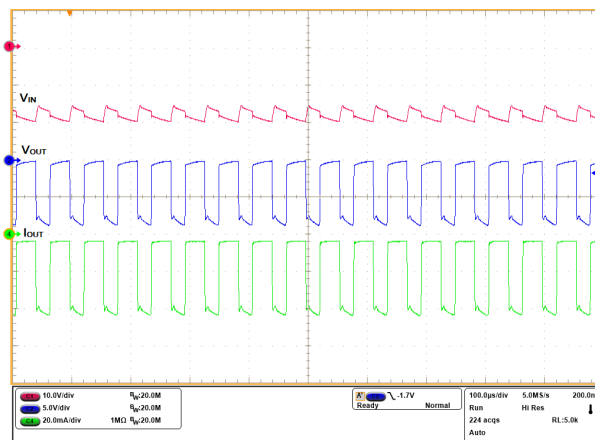
In case of over-voltage, under-voltage and miswiring events on IN and OUT pins, voltages exceeding Absolute Maximum Ratings (see [Specifications](#)) for IN and OUT Pins can damage the device. [Figure 8-11](#) and [Figure 8-12](#) illustrate the output and input under-voltage protection in TPS2661x devices.





+Vs = 15 V, -Vs = -15 V, R_{OUT} = 250 Ω, V_{IN} = 21 V

Figure 8-13. Thermal Protection During Loop Testing for I_{LOOP} > 0



+Vs = 15 V, -Vs = -15 V, R_{OUT} = 250 Ω, V_{IN} = -21 V

Figure 8-14. Thermal Protection During Loop Testing for I_{LOOP} < 0

8.3.5.1 Supply Sensing with VSNS For Loop Power Mode (TPS26610)

For the TPS26610 device, the set-point for transition to loop power mode can be set by connecting resistors (R1, R2) from +Vs pin to VSNS pin and GND pin as shown in [Figure 8-15](#). The set-point can be calculated as per [Table 8-1](#). It is recommended to use resistors R1 and R2 for supply sensing when voltage across burden resistor (I_{LOOP} × R_{Burden}) is more than 1.8 V. If VSNS is left open or floating, TPS26610 device transitions to loop power mode when +Vs is less than 1.8 V.

Table 8-1. Supply Sensing with VSNS for Loop Power Mode

Device Power Mode	+Vs Voltage
±Vs Supplies	+Vs ≥ V _(SNSR) × (R1 + R2)/R2 ⁽¹⁾
Loop Power	+Vs ≤ V _(SNSF) × (R1 + R2)/R2 ^{(1) (2)}

(1) Use (R1 + R2) ≤ (+Vs)/(45 µA). For V_(SNSR) and V_(SNSF) values, see [Electrical Characteristics](#)

(2) Keep V_(SNSF) × (R1 + R2)/R2 > (I_{LOOP} × R_{Burden})

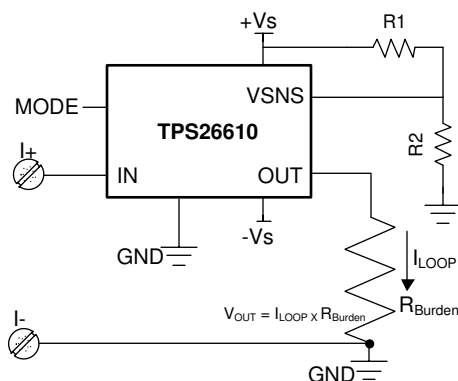
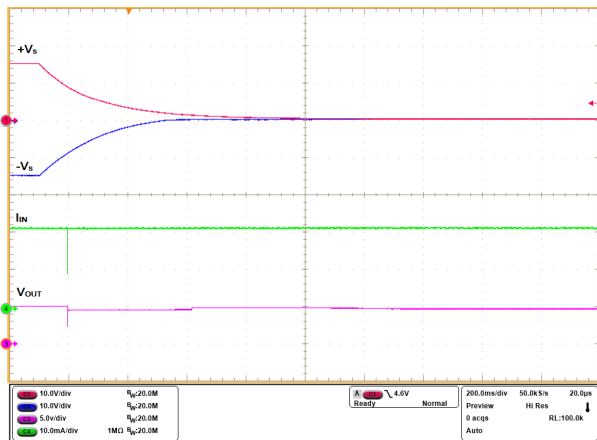
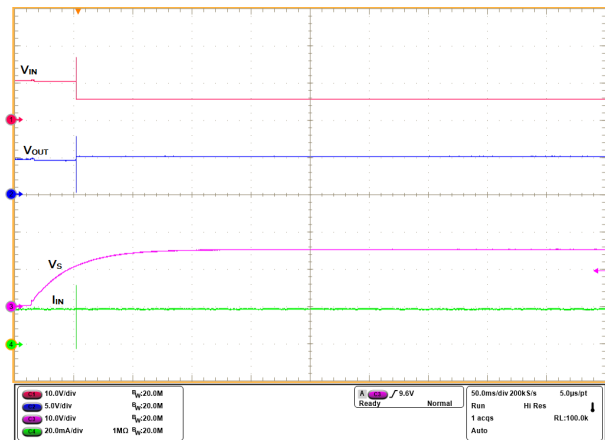


Figure 8-15. Supply Sensing with VSNS



+Vs = 15 V, -Vs = -15 V, $R_{OUT} = 250 \Omega$, MODE = GND

Figure 8-16. Transition to Loop Power with $R_1 = 47 \text{ k}\Omega$ and $R_2 = 6.8 \text{ k}\Omega$ for Supply Sensing



+Vs = 15 V, -Vs = -15 V, $R_{OUT} = 250 \Omega$, MODE = GND

Figure 8-17. Transition to $\pm V_s$ Supplies Power with $R_1 = 47 \text{ k}\Omega$ and $R_2 = 6.8 \text{ k}\Omega$ for supply Sensing

8.3.6 Enable Control (TPS26611 and TPS26612)

TPS26611 and TPS26612 devices feature an EN pin for externally controlling the device through a GPIO pin. To enable the device, EN pin can be left floating. It is internally pulled up with $V_{(EN)}$.

EN can also be made high with external voltage more than $V_{(ENR)}$ but less than or equal to 5 V. The internal FETs are turned off when EN is pulled below $V_{(ENF)}$. EN pin can source and sink a current of $I_{(EN_LKG)}$. See [Electrical Characteristics](#) for $V_{(ENF)}$, $V_{(ENR)}$ and $I_{(EN_LKG)}$. The EN feature of TPS2661x helps the system designer to design universal voltage and current analog inputs / outputs where a lot of pin multiplexing options are made available to the end user. For turn-on and turn-off delay with EN pin, see $t_{ON_EN_dly}$ and $t_{OFF_EN_dly}$ in [Timing Requirements](#). [Figure 8-19](#) and [Figure 8-20](#) illustrate the turn-on and turn-off control with enable pin.

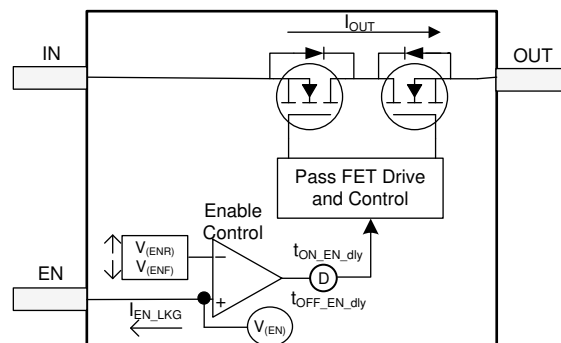


Figure 8-18. Enable Control

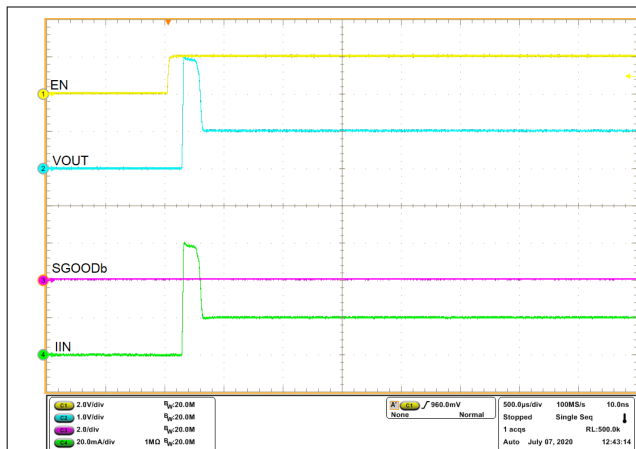


Figure 8-19. Turn-On with EN Pin

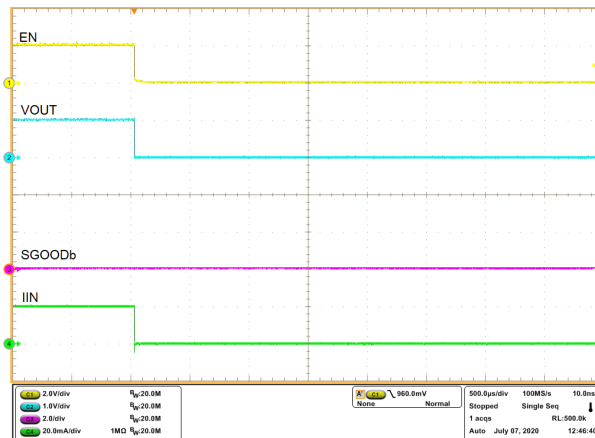


Figure 8-20. Turn-Off with EN Pin

8.3.7 Signal Good Indicator ($\overline{\text{SGOOD}}$)

The TPS2661x provides an indication of the current signal flowing through pass FETs on the $\overline{\text{SGOOD}}$ pin. Whenever the device is in normal operating condition, the $\overline{\text{SGOOD}}$ gives a signal LOW output. However in below cases when the device is outside normal operating condition, the $\overline{\text{SGOOD}}$ pin goes HIGH:

- Device current is $> I_{OL}$ (32-mA typical)
- OUT goes outside +Vs/-Vs supply or IN goes below -Vs supply rail
- Device shuts down due to thermal limit or current limit

The $\overline{\text{SGOOD}}$ pin is also capable of driving an external LED to give a visual indication whenever the system is outside normal operating conditions.

The $\overline{\text{SGOOD}}$ pin sourcing current is derived from +Vs supply rail. For de-glitch delays in assertion and de-assertion of $\overline{\text{SGOOD}}$, see $T_{\text{SG_Deglitch}}$ in [Timing Requirements](#) in Specifications.

8.4 Device Functional Modes

The device can provide higher current up to $2 \times I_{OL}$ for short durations. MODE pin of the device configures the behavior of the device for higher current. [Table 8-2](#) and [Figure 8-21](#) describe the device behavior in different modes for $I_{OL} > 0$.

With MODE = GND, the device limits the current to I_{OL} value for $I_{OUT} > I_{OL}$.

With MODE = OPEN, the device limits the output current as:

- For $I_{OL} < I_{OUT} < 2 \times I_{OL}$, the device allows current up to $2 \times I_{OL}$ for a duration of $t_{OL_Pulse_Expiry}$ and then limits the current to I_{OL} value for a duration t_{OL_Expiry} .
- For $2 \times I_{OL} < I_{OUT} < I_{(FASTRIP)}$, the device limits the current $2 \times I_{OL}$ value and for a duration of $t_{OL_Pulse_Expiry}$ and then limits the current to I_{OL} value for a duration t_{OL_Expiry} .

After the completion of t_{OL_Expiry} period, the device goes into auto-retry.

With MODE = 180 k Ω , the device limits the output current as:

- For $I_{OL} < I_{OUT} < 2 \times I_{OL}$, the device allows current up to $2 \times I_{OL}$ for a duration of t_{OL_Extend} and then limits the current to I_{OL} value for a duration t_{OL_Expiry} .
- For $2 \times I_{OL} < I_{OUT} < I_{(FASTRIP)}$, the device limits the current $2 \times I_{OL}$ value and for a duration of $t_{OL_Pulse_Expiry}$ and then limits the current to I_{OL} value for a duration t_{OL_Expiry} .

After the completion of t_{OL_Expiry} period, the device goes into auto-retry. If the device heats up during overload and the device temperature exceeds $T_{(TSD)}$ value, the device turns off the internal pass FETs. As the device cools down and its temperature goes below $[T_{(TSD)} - T_{(TSDHyst)}]$ value, the device goes into auto-retry.

Table 8-2. Device Operation Under Different MODE Configurations for $I_{OL} > 0$

MODE Pin Configuration	$I_{OUT} < I_{OL}$ (32 mA)	I_{OL} (32 mA) $< I_{OUT} < 2 \times I_{OL}$ (60 mA)	$2 \times I_{OL}$ (60 mA) $< I_{OUT} < I_{(FASTRIP)}$	Auto Retry Time
Shorted to GND	Current flows normally	Current limited to I_{OL} for a duration of t_{OL_Expiry} (100 ms). t_{OL_Expiry} (100 ms) timer starts when I_{OUT} exceeds I_{OL} .	Current limited to I_{OL} for a duration of t_{OL_Expiry} (100 ms). t_{OL_Expiry} (100 ms) timer starts when I_{OUT} exceeds I_{OL} .	t_{RETRY1} (800 ms)
Open	Current flows normally	Device allows current for $t_{OL_Pulse_Expiry}$ (50 ms) time after which it is limited to I_{OL} for t_{OL_Expiry} (100 ms) time and then auto retry. $t_{OL_Pulse_Expiry}$ (50 ms) timer starts when I_{OUT} exceeds I_{OL} .	Current limited to $2 \times I_{OL}$ for $t_{OL_Pulse_Expiry}$ (50 ms) time after which it is limited to I_{OL} for t_{OL_Expiry} (100 ms) time and then auto retry. $t_{OL_Pulse_Expiry}$ (50 ms) timer starts when I_{OUT} exceeds I_{OL} .	t_{RETRY1} (800 ms)
180 kΩ from MODE to GND	Current flows normally	Device allows current for t_{OL_Extend} (5 s) time after which it is limited to I_{OL} for t_{OL_Expiry} (100 ms) time and then auto retry. t_{OL_Extend} (5 s) timer starts when I_{OUT} exceeds I_{OL} .	Current limited to $2 \times I_{OL}$ for $t_{OL_Pulse_Expiry}$ (50 ms) time after which it is limited to I_{OL} for t_{OL_Expiry} (100 ms) time and then auto retry. $t_{OL_Pulse_Expiry}$ (50ms) timer starts when I_{OUT} exceeds I_{OL} .	t_{RETRY2} (1.6 s)

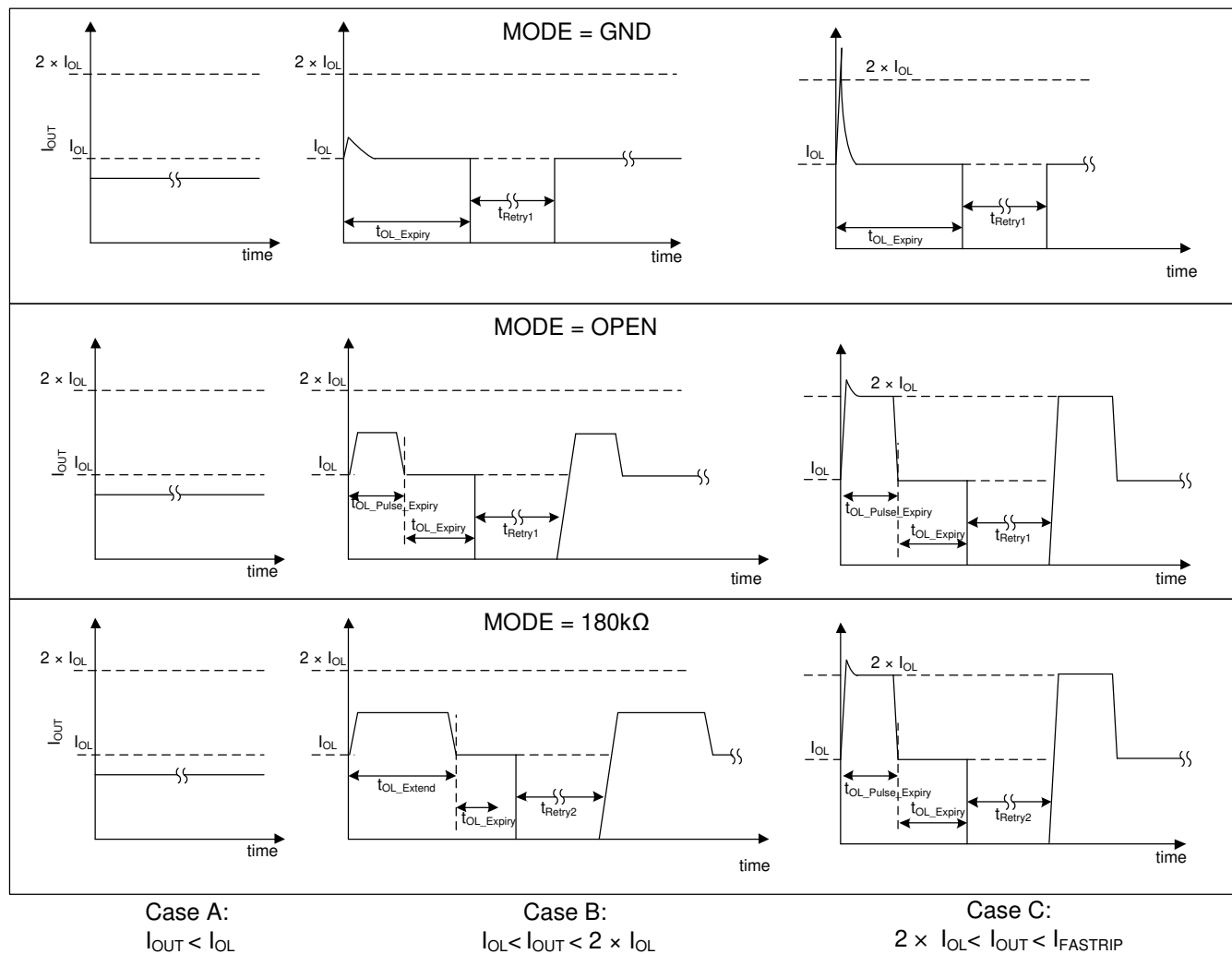
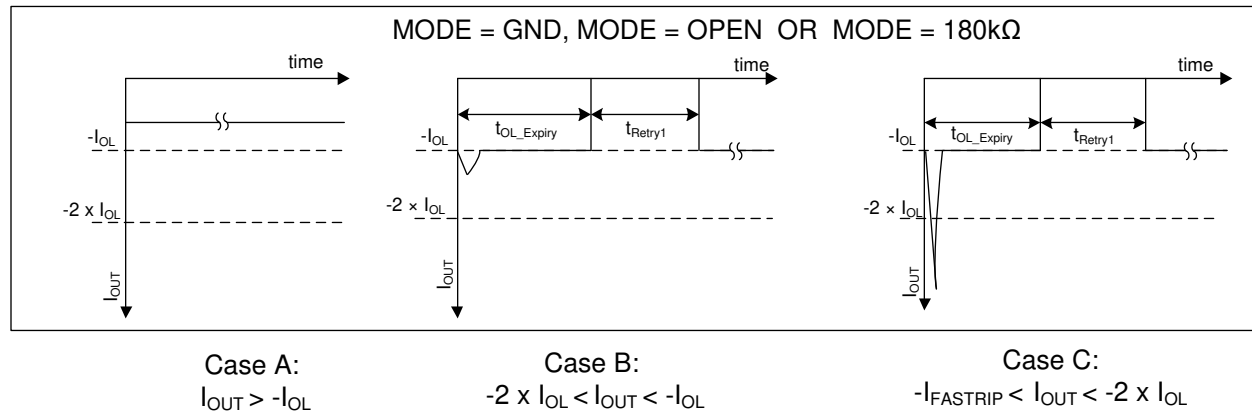


Figure 8-21. Device Operation Under Different MODE Configurations for $I_{OL} > 0$

Table 8-3 and Figure 8-22 describe the device behavior in different modes for $I_{OL} < 0$.

Table 8-3. Device Operation Under Different MODE Configurations for $I_{OL} < 0$

MODE Pin Configuration	$I_{OUT} > -I_{OL}$ (–32mA)	$-2 \times I_{OL}$ (–60 mA) $< I_{OUT} < -I_{OL}$ (–32mA)	$-I_{FASTrip} < I_{OUT} < -2 \times I_{OL}$ (–60 mA)	Auto Retry Time
Shorted to GND or Open or 180 kΩ from MODE to GND	Current flows normally	Current limited to I_{OL} for a duration of t_{OL_Expiry} (100 ms). t_{OL_Expiry} (100 ms) timer starts when I_{OUT} exceeds I_{OL} .	Current limited to I_{OL} for a duration of t_{OL_Expiry} (100ms). t_{OL_Expiry} (100ms) timer starts when I_{OUT} exceed I_{OL} .	t_{RETRY1} (800 ms)

**Figure 8-22. Device Operation Under Different MODE Configurations for $I_{OL} < 0$**

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The TPS2661x is an industrial current loop protector, providing a robust signal line protection in a wide range of industrial and automations systems. It is suitable for protection of all kinds of current loops like the 4 - 20-mA or ± 20 -mA current loops. TPS26610 is suitable for protection in current inputs whereas TPS26611 is suitable for protection in multiplexed V/I inputs.

TPS26612 is suitable for protection in power supply of two wire current transmitters. With disabled auto-retry time for first overload event, TPS26612 enables start-up of power hungry transmitters requiring higher start up current for longer durations.

TPS26611 and TPS26612 devices can be also used to protect voltage outputs or digital communication signals like UART from miswiring of power supplies at these outputs. The device breaks the signal path by turning off the FETs when there is a voltage higher than supply voltage and thus keeping the system protected.

TPS2661x provides complete protection from industrial surge transients (IEC61000-4-5) and provides immunity from industrial fast transients (IEC61000-4-4) for signal lines.

9.2 Typical Application: Analog Input Protection for Current Inputs with TPS26610

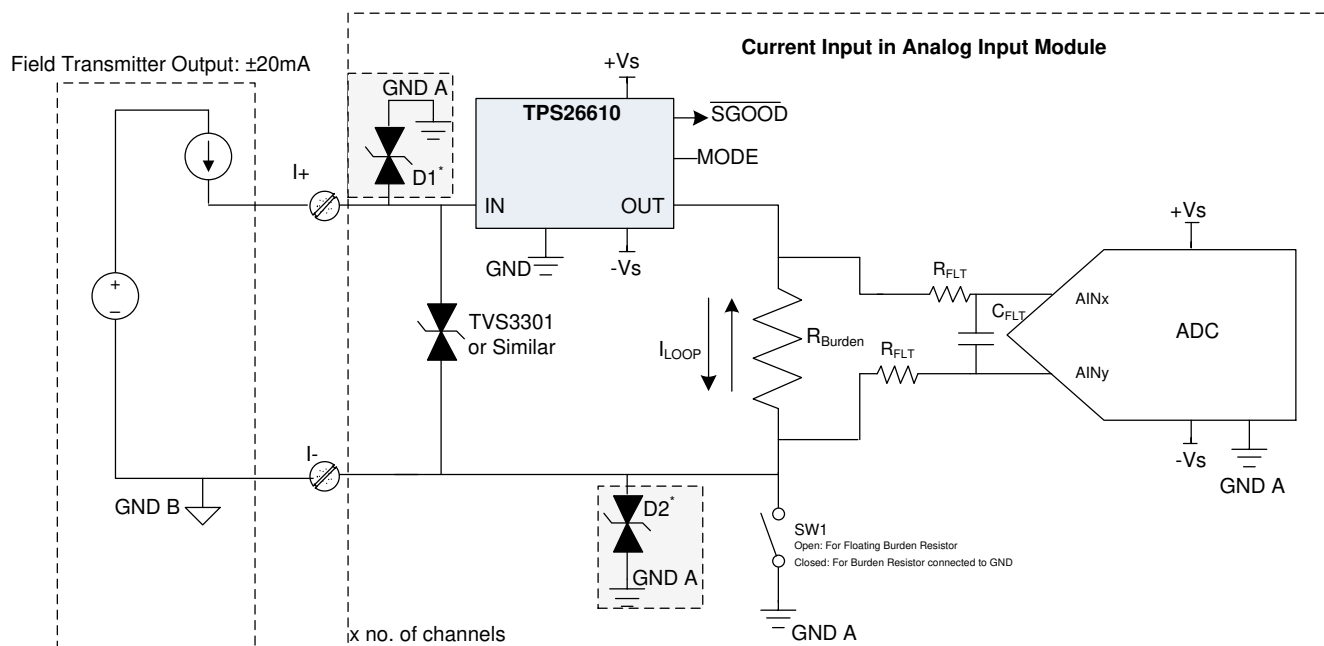


Figure 9-1. Current Input Protection in AI Module

A. TVS Diodes D1*, D2* are required for protection from surge transients (IEC61000-4-5) when burden resistor is floating (SW1 = Open).

TPS26610 can be used for protection of current inputs in an Analog Input module as shown in Figure 9-1. The current signal is measured by ADC across R_{burden} . Bipolar current limit of ± 32 mA ensures that the precision burden resistor as well as the ADC front end stays well protected against any unwanted voltages or currents caused due to faulty transmitter or miswiring. High Voltage rating of IN pin of TPS26610 ensures that it also

protects the system from surge and EFT events as well. For reverse current blocking (OUT to IN), connect burden resistor to GND (SW1 = Closed) and used single supply (+Vs,GND) with TPS26610.

9.2.1 Design Requirements

Table 3 shows the Design Requirements for current input protection with TPS26610.

Table 9-1. Design Requirements

DESIGN PARAMETER		EXAMPLE VALUE
$I_{(IN)}$	Input current	± 20 mA
$V_{(IN)}$	Input voltage	$-V_s$ to 50 V
$V_{(OUT)}$	OutPut voltage	$\pm V_s$
$I_{(LIM)}$	Current limit	± 30 mA
R_{Burden}	Burden resistance	50 to 250 Ω

9.2.2 Detailed Design Procedure for Current Inputs with TPS26610

9.2.2.1 Selecting $\pm V_s$ Supplies for TPS26610

Select the $\pm V_s$ supplies for TPS2661x devices higher than absolute analog input voltage for ADC inputs.

TPS2661x devices have under-voltage and over-voltage protection on OUT pin and the internal FETs are turned off if OUT pin has voltage higher than $+V_s$ or lower than $-V_s$.

TPS2661x devices also have under-voltage protection on IN pin and the internal FETs are turned off if IN pin has a voltage lower than $-V_s$. See [External Power Supply](#) for using unipolar or bipolar supply with TPS2661x.

9.2.2.2 Selecting R_{Burden}

The value of R_{burden} should be selected to meet the analog the input range of the ADC for the loop current range. In case of miswiring faults to field supplies, the maximum current and power dissipated in R_{burden} is decided by MODE configuration of TPS26610 device.

Table 9-2. Selection of R_{burden}

R_{burden} (Ω)	MODE Configuration	Maximum Current in R_{burden} (mA)	Maximum Power Dissipated in R_{burden} (mW)
50	MODE = GND	40	80
100	MODE = GND	40	160
250	MODE = GND	40	400
50	MODE = OPEN or 180 k Ω	70	245 ⁽¹⁾
100	MODE = OPEN or 180 k Ω	70	490 ⁽¹⁾
250	MODE = OPEN or 180 k Ω	70	1225 ⁽¹⁾

(1) Power dissipated only for a pulse duration of 50 ms

9.2.2.3 Selecting MODE Configuration for TPS26610

For minimum power dissipation in burden resistor, use MODE = GND. See [Device Functional Modes](#) for selecting the mode configuration.

9.2.3 Application Performance Plots for Current Inputs with TPS26610

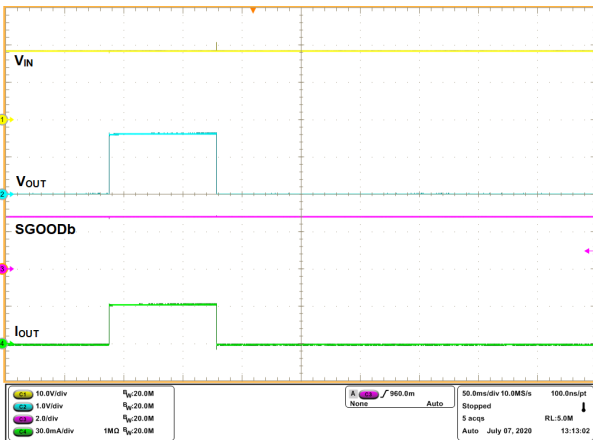


Figure 9-2. Current Limiting with MODE = GND, $R_{burden} = 50\ \Omega$

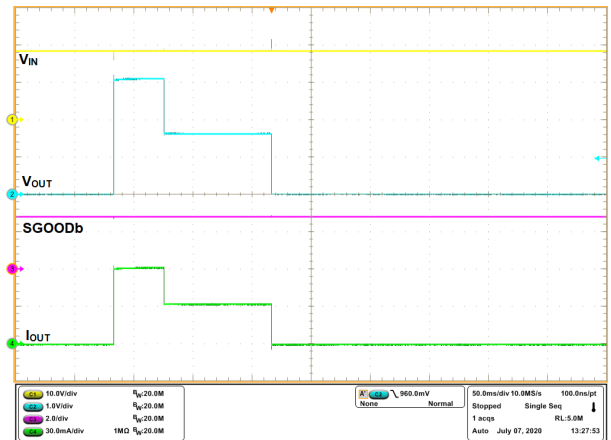


Figure 9-3. Current Limiting with MODE = OPEN, $R_{burden} = 50\ \Omega$

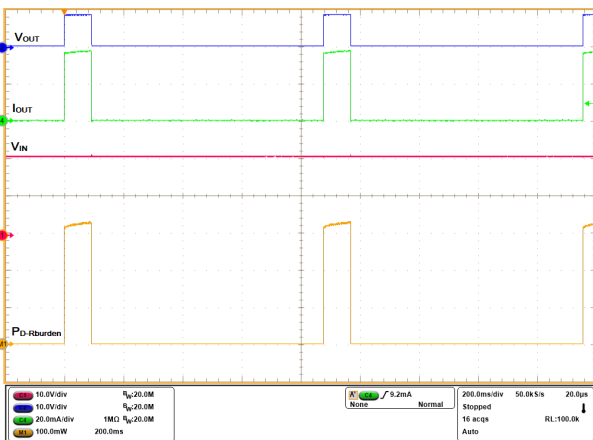


Figure 9-4. Power Dissipation in $R_{burden} = 250\ \Omega$ with MODE = GND

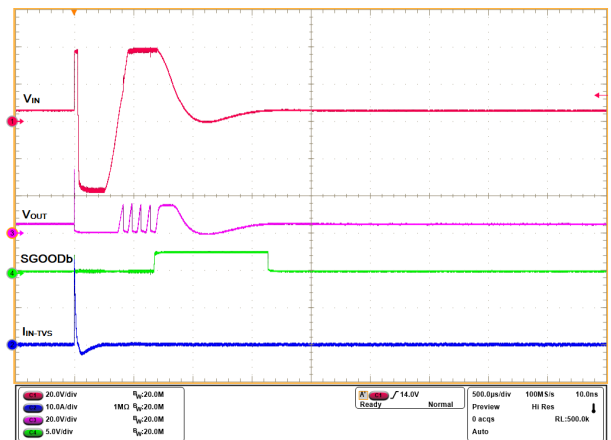


Figure 9-5. IEC61000-4-5 (+1 kV, 42 Ω) Signal Line Surge immunity with TVS3301 at IN

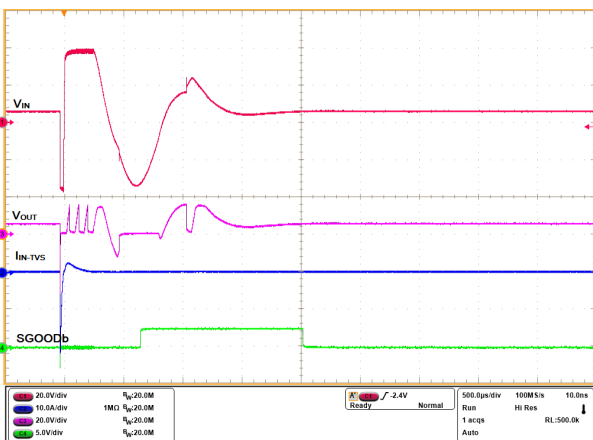


Figure 9-6. IEC61000-4-5 (-1 kV, 42 Ω) Signal Line Surge immunity with TVS3301 at IN

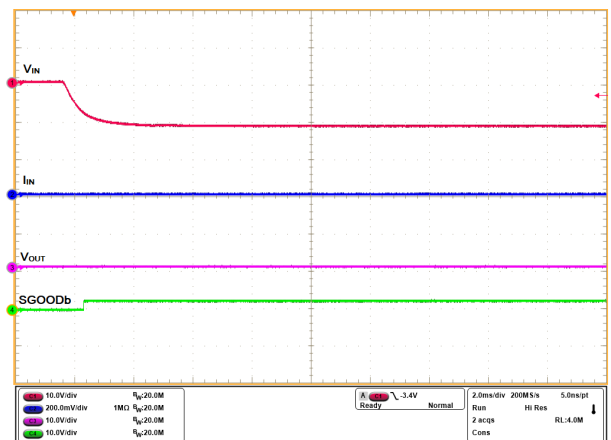


Figure 9-7. Reverse Current blocking with $V_{IN} = -12\text{ V}$, $-V_S = \text{GND}$ and SW1 = Closed

9.3 Typical Application: Analog Input Protection for Multiplexed Current and Voltage Inputs with TPS26611

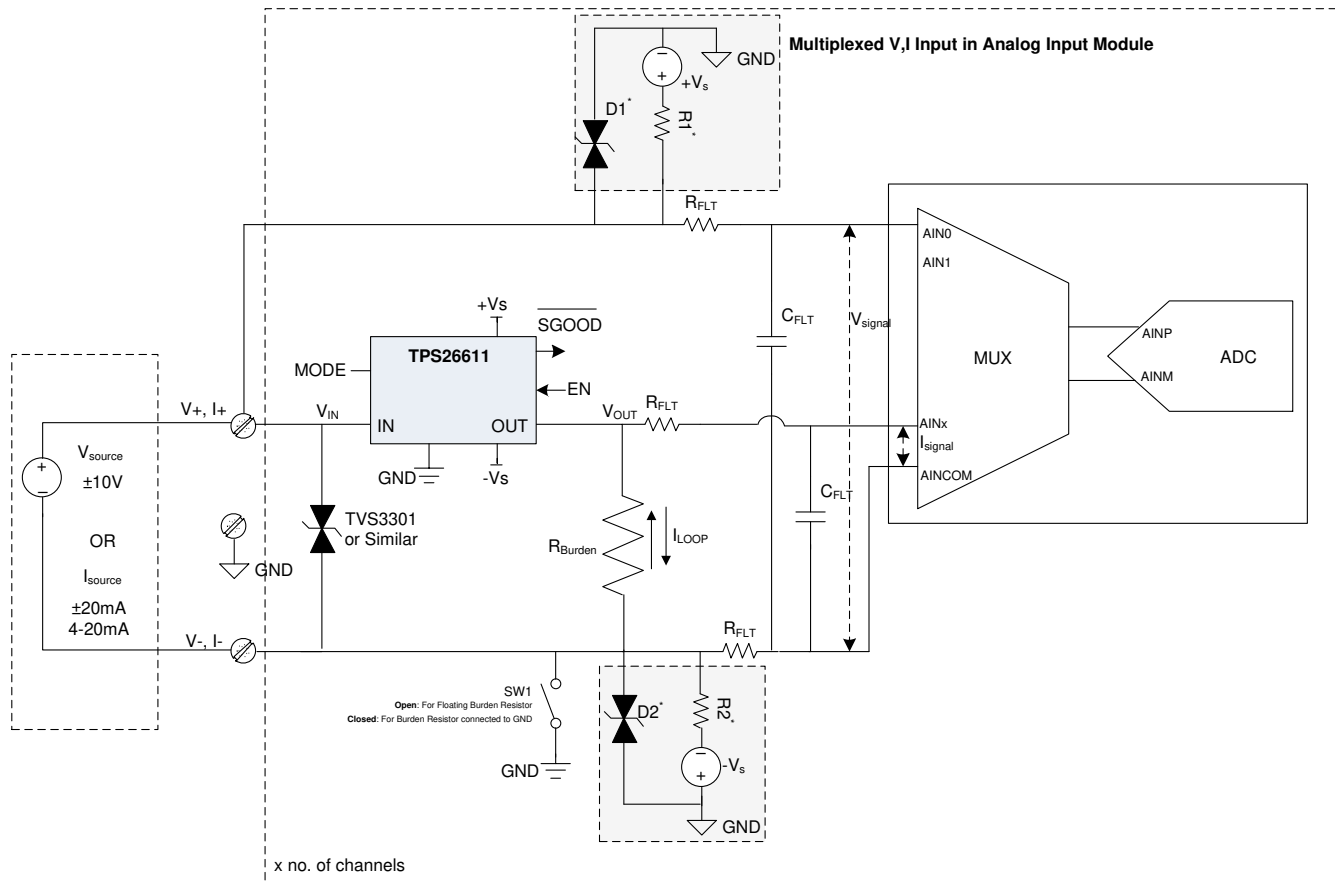


Figure 9-8. Protection for Multiplexed V/I Inputs in AI Module

- A. Bias Resistors R1*, R2* are required for setting the common mode voltage for voltage input (EN = 0) when burden resistor is floating (SW1 = Open).
- B. Diodes D1*, D2* are required surge protection when burden resistor is floating (SW1 = Open).

TPS26611 can be used for protection of multiplexed inputs in an Analog Input module as shown in [Figure 9-8](#). For this configuration, connect the IN pin of TPS26611 to one channel of the ADC for voltage measurement and connect OUT pin of TPS26611 to the other channel of ADC for current measurement. EN pin of TPS26611 can be used to switch between current and voltage measurements. With EN = 0, the internal FETs of TPS26611 are turned off and voltage signal can be measured by ADC between AIN0 and AINCOM pins. Whereas with EN = 1, the internal FETs of TPS26611 are turned on and current signal can be measured by ADC between AINx and AINCOM pins.

9.3.1 Design Requirements

Table 9-3. Design Parameters

PARAMETER	VALUE
Input Current (I_{IN})	± 20 mA
Input Voltage (V_{IN})	± 10 V
Current Limit for (I_{IN})	± 32 mA
R_{Burden}	50 to 250 Ω

9.3.2 Detailed Design Procedure for Analog Input Protection for Multiplexed Current and Voltage Inputs with TPS26611

9.3.2.1 Selecting $\pm V_s$ Supplies for TPS26611

See V_s supply selection in [Typical Application: Analog Input Protection for Current Inputs with TPS26610](#).

9.3.2.2 Selecting MODE Configuration for TPS26611

For minimum power dissipation in burden resistor, use MODE = GND. See [Device Functional Modes](#) for selecting the mode configuration.

9.3.2.3 Selecting Bias Resistors R1, R2 for Setting Common Mode Voltage for Voltage Inputs

For setting the common mode voltage with floating burden resistor (SW1 = Open), bias resistor R1 and R2 are required.

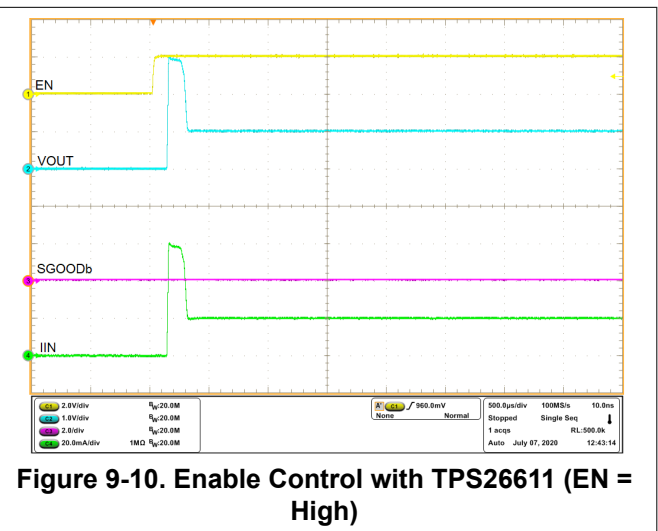
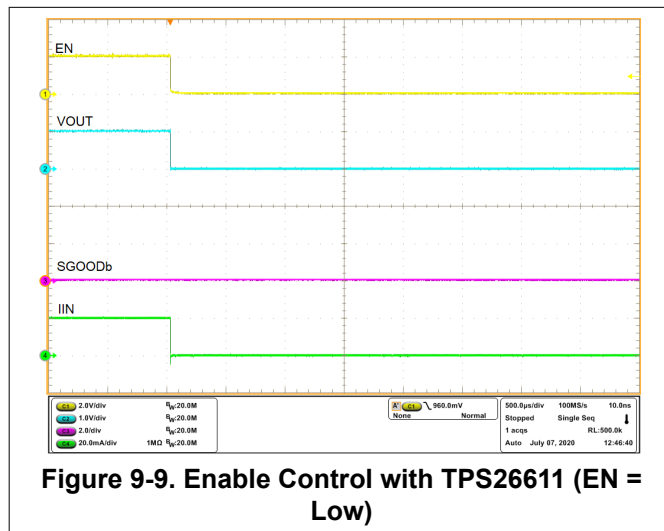
Resistors R1, R2 provide low impedance path for off state (EN = 0) leakage currents from IN and OUT pins of TPS26611. R1, R2 are selected to keep bias current less than 4 μA through these resistors for current measurements with R_{burden} (EN = 1).

Table 9-4. Selection of Bias Resistors R1, R2

Analog Input Voltage for ADC	$\pm V_s$ Supplies	Bias Current Through R1, R2	R1	R2
$\pm 10\text{ V}$	$\pm 15\text{ V}$	$< 4\text{ }\mu\text{A}$	1.39 to 1.66 $\text{M}\Omega$	6.67 to 6.94 $\text{M}\Omega$
$\pm 12.5\text{ V}$	$\pm 15\text{ V}$	$< 4\text{ }\mu\text{A}$	1.35 to 1.71 $\text{M}\Omega$	6.62 to 6.98 $\text{M}\Omega$
$\pm 15\text{ V}$	$\pm 18\text{ V}$	$< 4\text{ }\mu\text{A}$	1.29 to 1.75 $\text{M}\Omega$	6.58 to 7.04 $\text{M}\Omega$

9.3.3 Application Performance Plots for V/I Inputs with TPS26611

In addition to current limiting, reduced power dissipation in burden resistor, reverse current blocking and surge protection illustrated in [Section 9.2.3](#), TPS26611 provides enable control for selecting between voltage and current inputs.



9.4 System Examples

9.4.1 Power Supply Protection of 2-Wire Transmitter with TPS26612

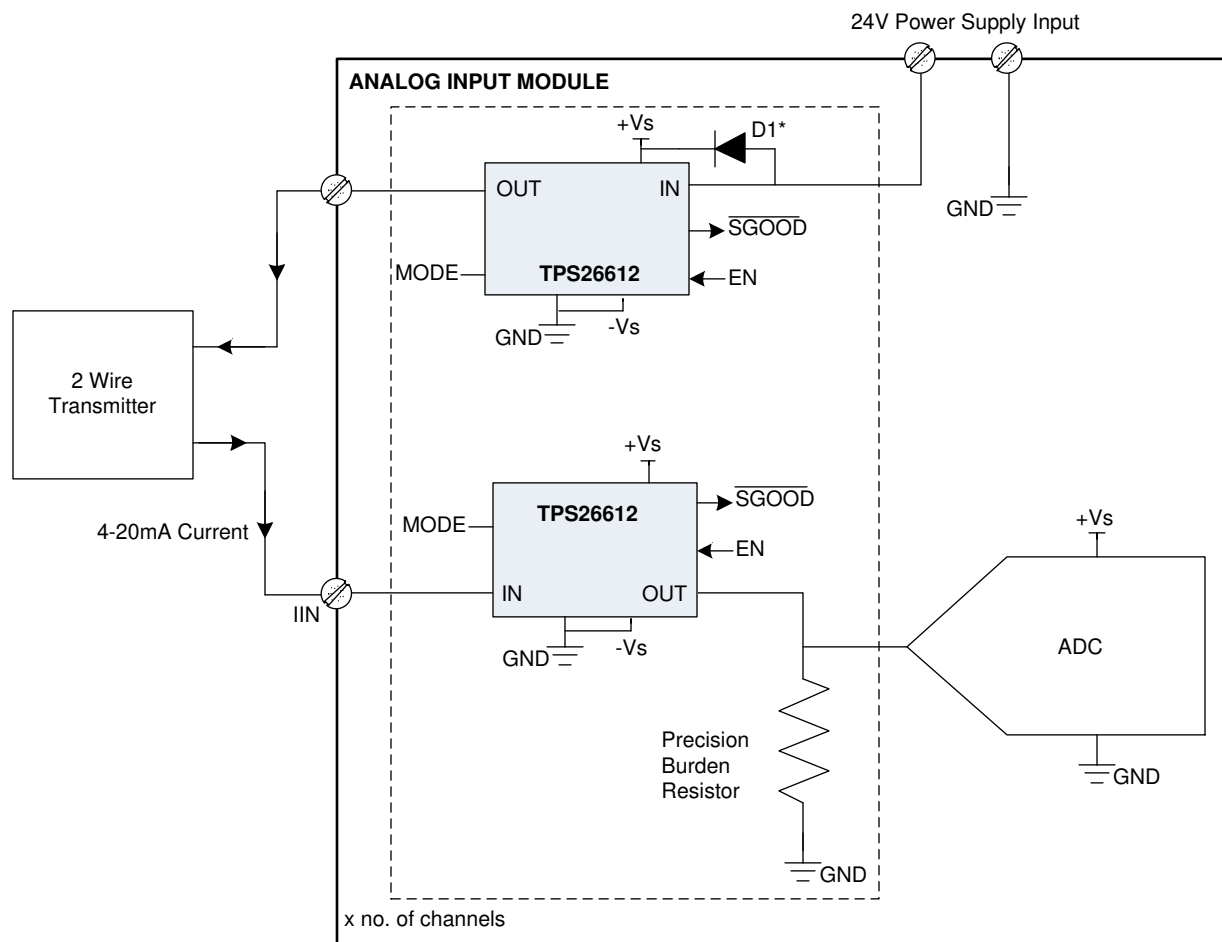
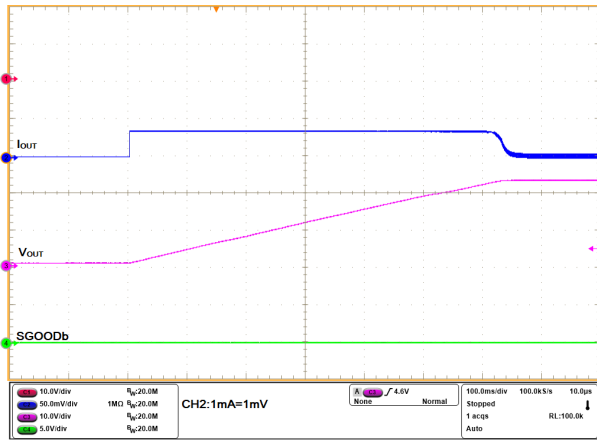


Figure 9-11. Power Supply Protection for 2-Wire Transmitter with TPS26612

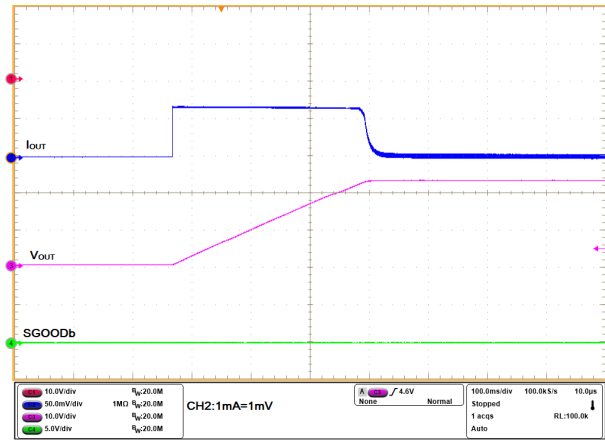
TPS26612 can be used for protection of power supply powering a two wire field transmitter as shown in [Figure 9-11](#). Connect an external signal diode (D1) from IN to +Vs pin of TPS26612 in case of external field supply to protect the system from miswiring. In case the supply is internal to the module and miswiring is not a possibility, the signal diode (D1) is not needed. TPS26612 device includes higher threshold for over-voltage protection on OUT to accommodate the voltage drop of diode (D1) between IN and +Vs.

TPS26612 has over-load expiry time (t_{OL_expiry}) disabled for the first overload fault after power-up up-to a duration of t_{AR_dis} (5 sec). With overload expiry time disabled, TPS26612 is able to power up 2-wire transmitters requiring higher start-up for longer durations (up-to 5 sec.). The current limit threshold (I_{OL} or $2 \times I_{OL}$) for start-up can be selected by MODE pin.



$V_{IN} = 24\text{ V}$, $C_{OUT} = 1\text{ mF}$

Figure 9-12. TPS26612: Startup of 2-Wire transmitter with MODE = GND, $I_{OUT} = 30\text{ mA}$

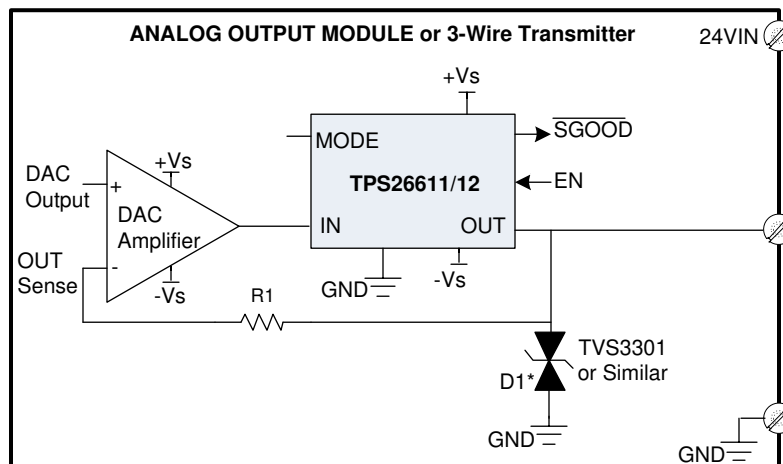


$V_{IN} = 24\text{ V}$, $C_{OUT} = 1\text{ mF}$

Figure 9-13. TPS26612: Startup of 2-Wire transmitter with MODE = Open, $I_{OUT} = 60\text{ mA}$

During the first overload fault, if the the junction temperature reaches T_{SD} , the device turns-off the internal FETs and turns on as the junction temperture goes below $[T_{TSD} - T_{TSDHyst}]$.

9.4.2 Protection of 3-Wire Transmitters and Analog Output Modules with TPS26611/12



Diode (D1) is required for Singal line Surge (IEC61000-4-5) protection.

Figure 9-14. Analog Output Protection with TPS26611 or TPS26612

TPS26611 or TPS26612 can be used for protection of the analog output a 3/4-wire transmitter and analog output module against any high voltage field miswiring as shown in [Figure 9-14](#). The OUT pin voltage is monitored with respect to the +Vs/-Vs supply voltages. If the OUT voltage goes outside the +Vs/-Vs supply rails, the FETs cutoff current conduction path and protects the whole system. The voltage at OUT pin of TPS2661x can be sensed by DAC amplifier to compensate for R_{ON} of TPS2661x

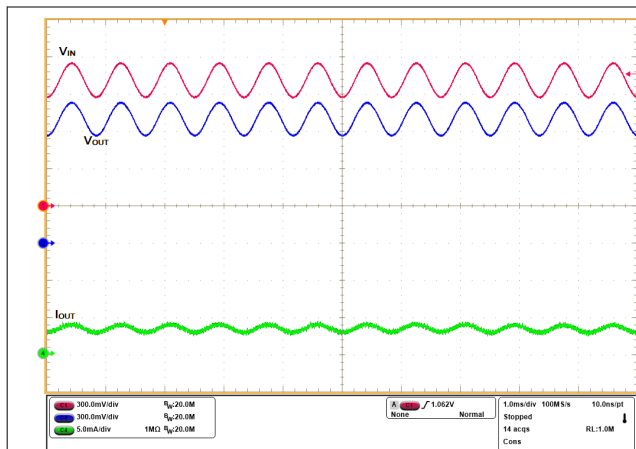


Figure 9-15. 1.2-kHz HART Signal Through TPS2661x with $R_{OUT} = 250\ \Omega$

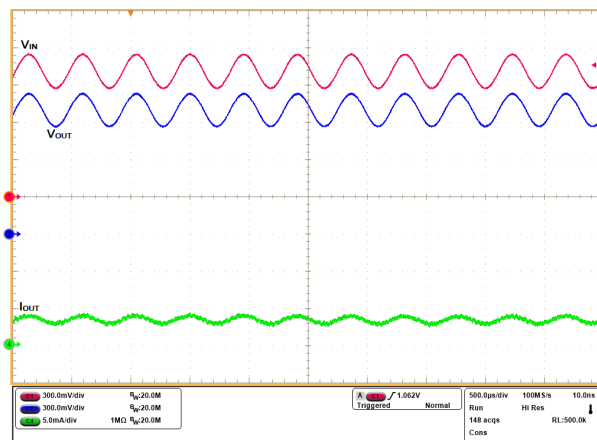


Figure 9-16. 2.2-kHz HART Signal Through TPS2661x with $R_{OUT} = 250\ \Omega$

9.4.3 UART IO Protection with TPS26611/12

TPS26611 or TPS26612 can be used for protection of UART IO lines as shown in [Figure 9-17](#). The OUT pin voltage is monitored with respect to the +Vs/-Vs supply voltages. If the OUT voltage goes outside the +Vs/-Vs supply rails, the FETs cutoff the current conduction path and protects the whole system.

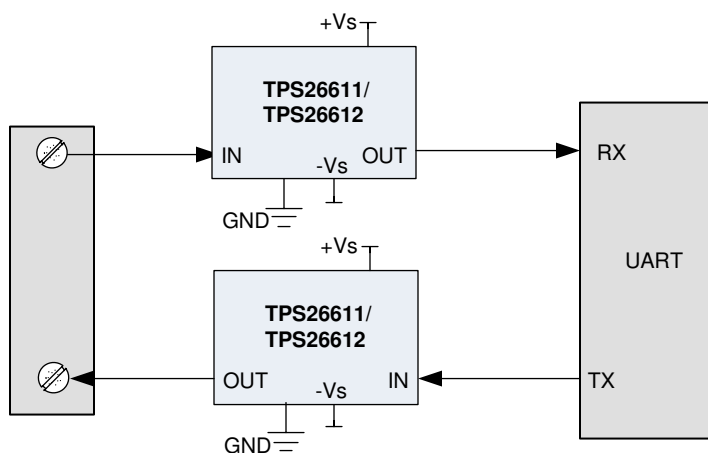


Figure 9-17. UART IO Protection

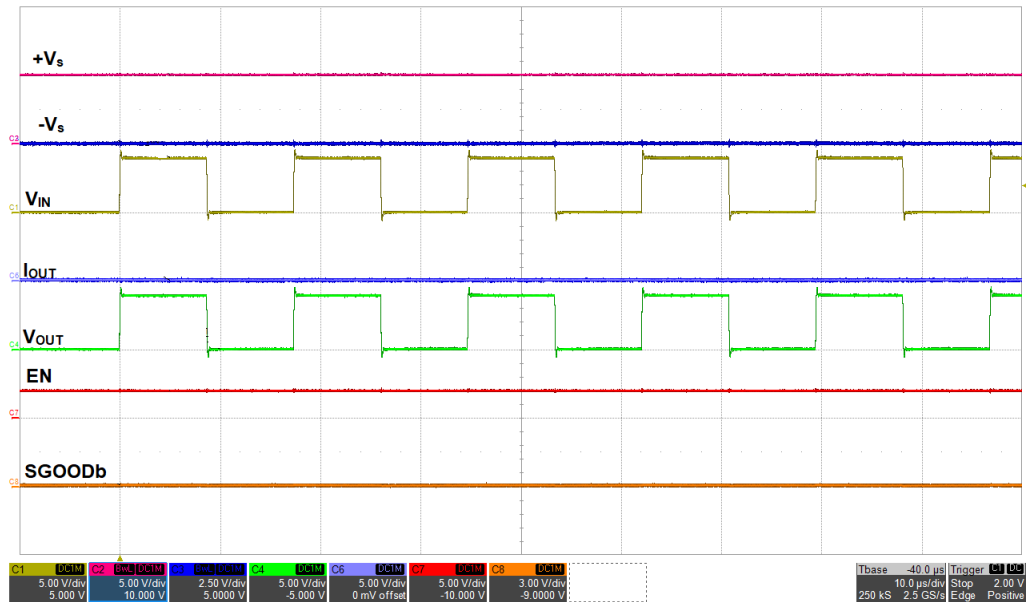


Figure 9-18. 115.2-Kbps UART Signal Through TPS2661x with V_s of 5 V

Figure 9-18 shows a UART signal of 115.2 Kbps through TPS2661x with amplitude of 4 V.

10 Power Supply Recommendations

Table 10-1. Power Supplies for TPS2661x Devices

Device	Dual Supply ($\pm V_s$)	Single Supply (+ V_s , GND)
TPS26610	+ V_s : 2.25 V to 30 V, - V_s : -20 V to 0 V	+ V_s : 3 V to 30 V, - V_s : GND
TPS26611	+ V_s : 2.25 V to 30 V, - V_s : -20 V to 0 V	+ V_s : 3 V to 30 V, - V_s : GND
TPS26612	+ V_s : 2.25 V to 30 V, - V_s : -20 V to 0 V	+ V_s : 4 V to 30 V, - V_s : GND

For operation with dual supplies, TPS2661x devices need a minimum difference of 3 V between + V_s and - V_s . For reverse current blocking with single supply, see [Reverse Current Blocking for Unipolar Current Inputs \(4 - 20 mA, 0 - 20 mA\)](#).

11 Layout

11.1 Layout Guidelines

- Keep the loop current power-path as short as possible.
- Place R_{MODE} resistor close to MODE and GND pins of the device.
- For protection from IEC61000-4-5 surge transients (Signal Lines) on input, place the TVS close to IN pin of the device.
- If power supplies for $\pm V_s$ are far from the device, place at-least 100-nF ceramic capacitors close to the device.
- Connect GND pin of the device to GND of $\pm V_s$ supplies.
- Route both terminals of R_{burden} differentially to ADC inputs (AINP, AINM).
- Keep EN and \overline{SGOOD} signal lines away from loop current to avoid digital noise.

11.2 Layout Example

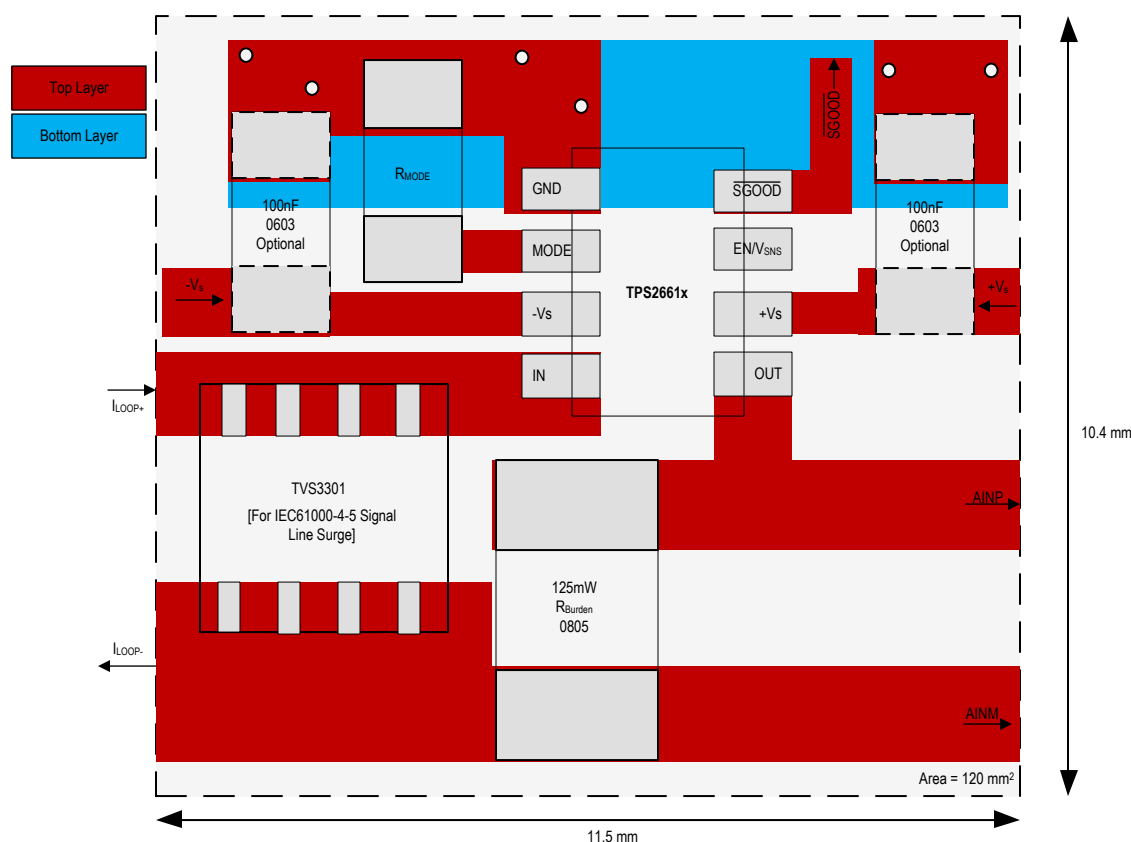


Figure 11-1. Layout Example

12 Device and Documentation Support

12.1 Documentation Support

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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12.4 Trademarks

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12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
PTPS26610DDFR	ACTIVE	SOT-23-THIN	DDF	8	3000	Non-RoHS & Non-Green	Call TI	Call TI	-40 to 125		Samples
PTPS26611DDFR	ACTIVE	SOT-23-THIN	DDF	8	3000	Non-RoHS & Non-Green	Call TI	Call TI	-40 to 125		Samples
PTPS26612DDFR	ACTIVE	SOT-23-THIN	DDF	8	3000	Non-RoHS & Non-Green	Call TI	Call TI	-40 to 125		Samples
TPS26610DDFR	ACTIVE	SOT-23-THIN	DDF	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2HSF	Samples
TPS26611DDFR	ACTIVE	SOT-23-THIN	DDF	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2HTF	Samples
TPS26612DDFR	ACTIVE	SOT-23-THIN	DDF	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2HUF	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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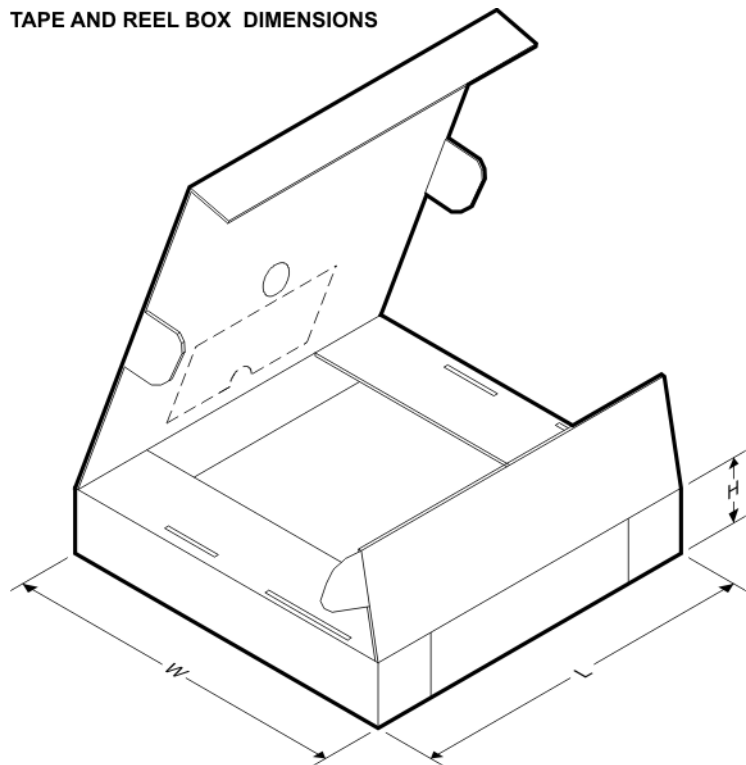
TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS26610DDFR	SOT-23-THIN	DDF	8	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS26611DDFR	SOT-23-THIN	DDF	8	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

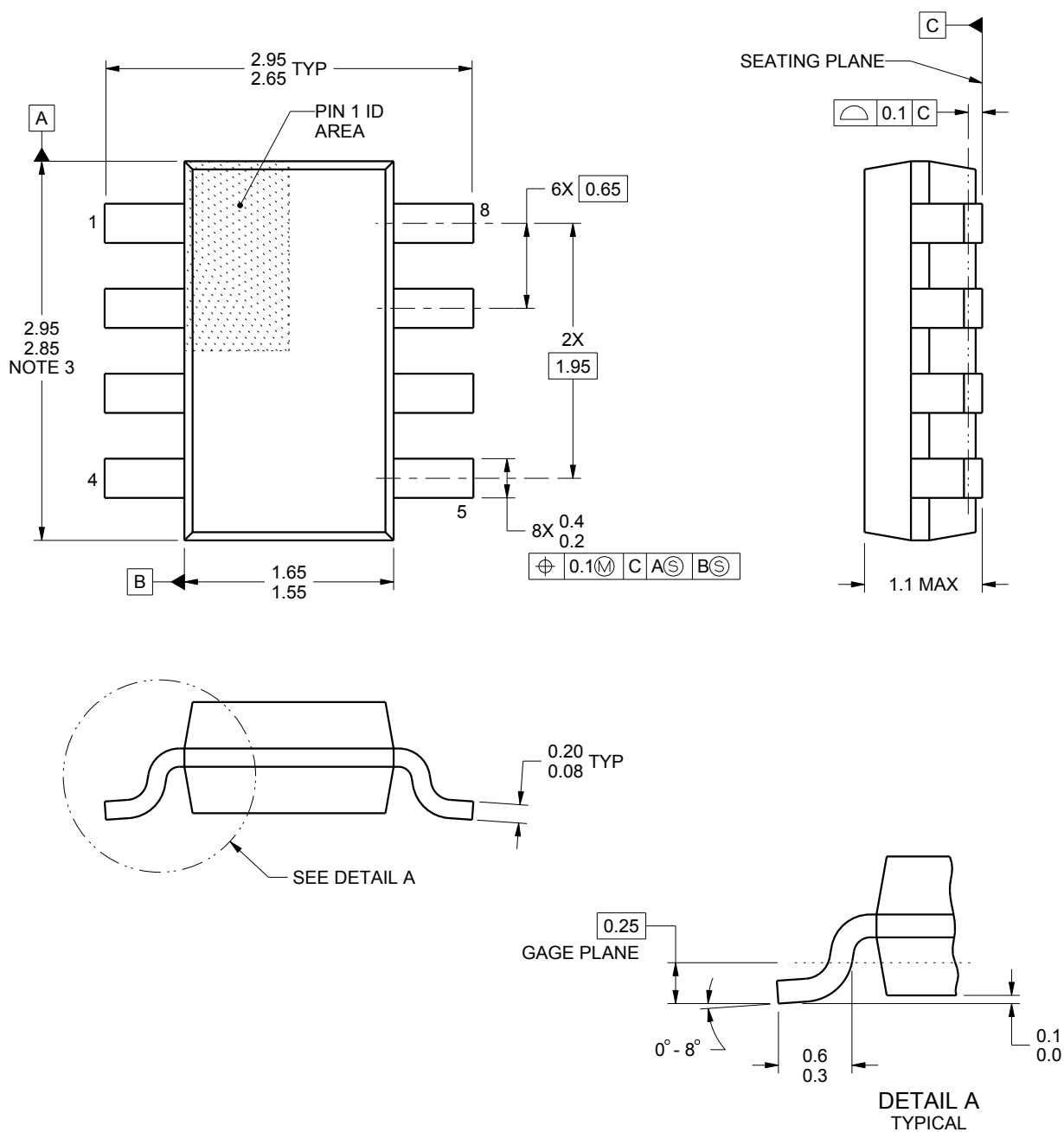
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS26610DDFR	SOT-23-THIN	DDF	8	3000	210.0	185.0	35.0
TPS26611DDFR	SOT-23-THIN	DDF	8	3000	210.0	185.0	35.0



PACKAGE OUTLINE

SOT-23 - 1.1 mm max height

PLASTIC SMALL OUTLINE



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NOTES:

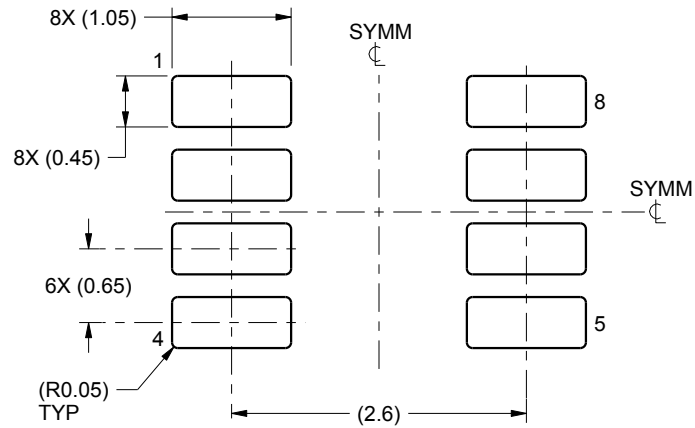
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.

EXAMPLE BOARD LAYOUT

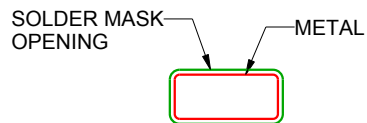
DDF0008A

SOT-23 - 1.1 mm max height

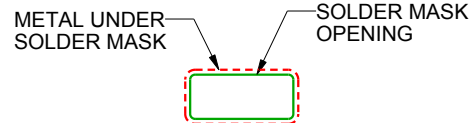
PLASTIC SMALL OUTLINE



LAND PATTERN EXAMPLE
SCALE:15X



NON SOLDER MASK
DEFINED



SOLDER MASK
DEFINED

SOLDER MASK DETAILS

4222047/B 11/2015

NOTES: (continued)

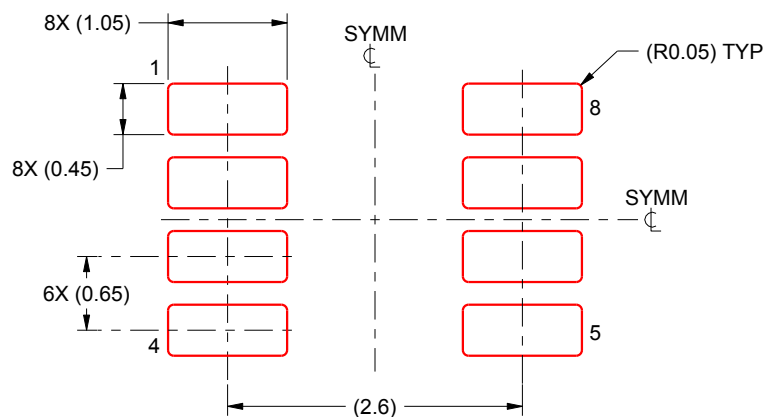
4. Publication IPC-7351 may have alternate designs.
5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DDF0008A

SOT-23 - 1.1 mm max height

PLASTIC SMALL OUTLINE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4222047/B 11/2015

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
7. Board assembly site may have different recommendations for stencil design.

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